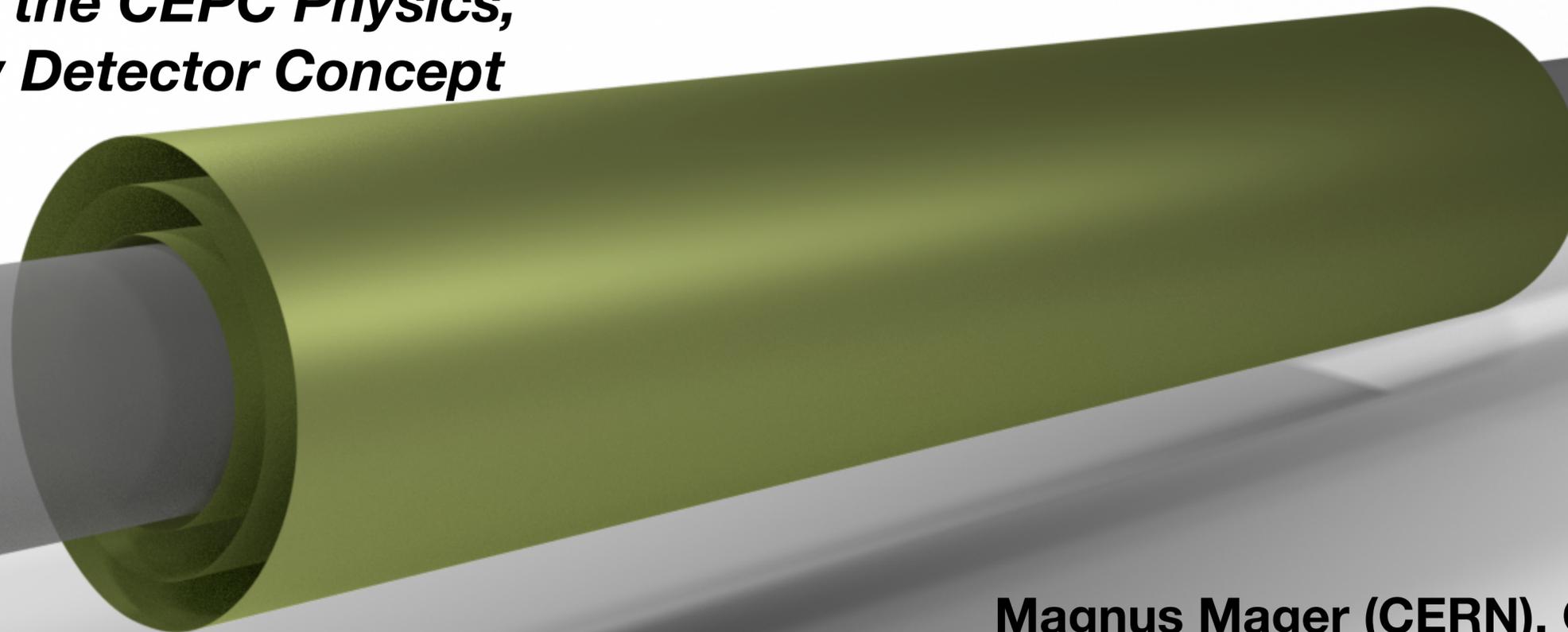


# **Bent CMOS sensor R&D for next-generation vertex detector *ALICE ITS3***

**Magnus Mager (CERN)**

*on behalf of the ALICE collaboration*

*Joint Workshop of the CEPC Physics,  
Software and New Detector Concept*



# Overview



## ▶ **ALICE ITS3**

- motivation, requirements, layout
- link to C3 Vertex Detector

## ▶ **bending MAPS**

- mechanics, test beams

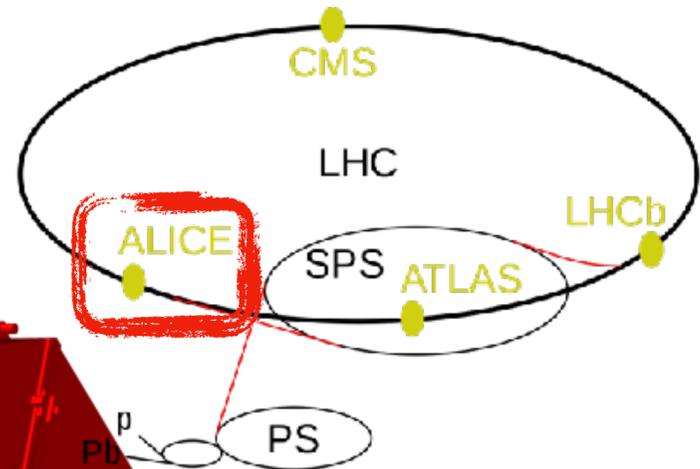
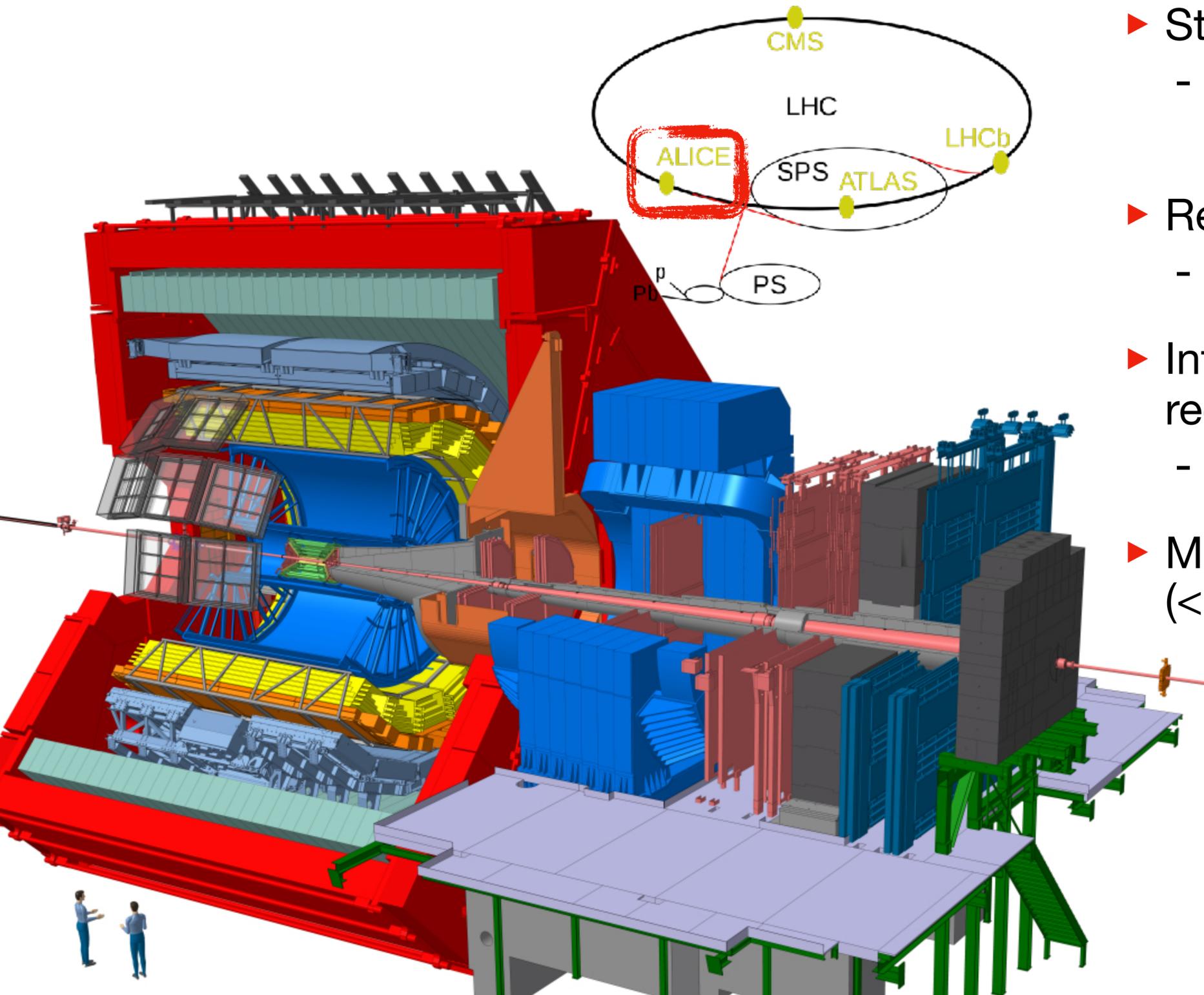
## ▶ **Sensor development in TPSCo 65nm CIS**

- results from prototypes, plans

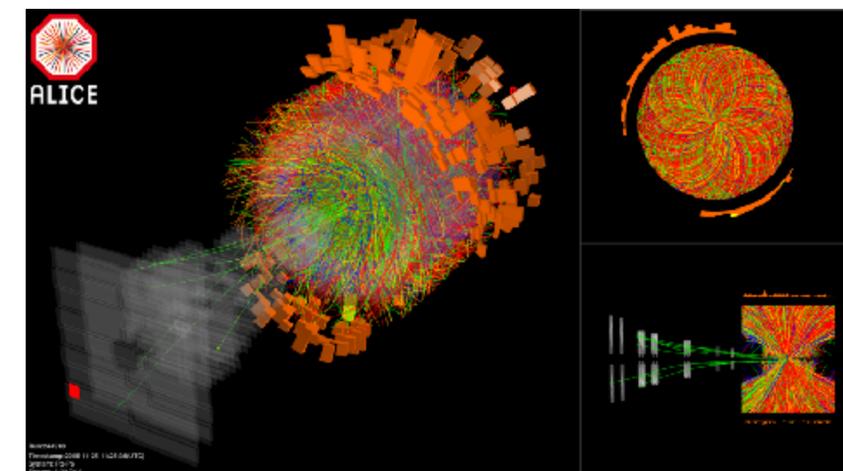
## ▶ **Outlook**

# ALICE

## Detector and main goals

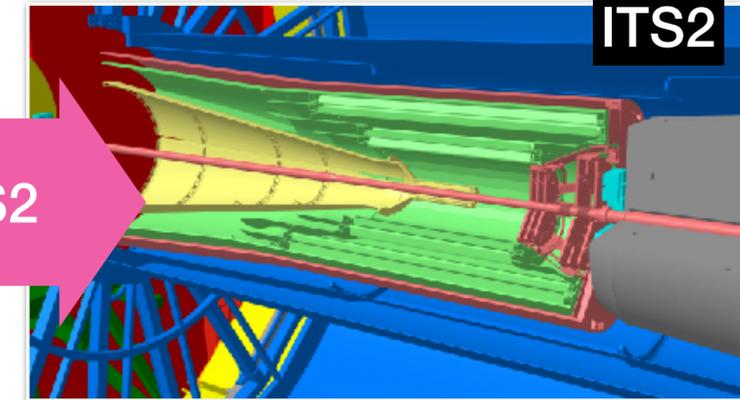
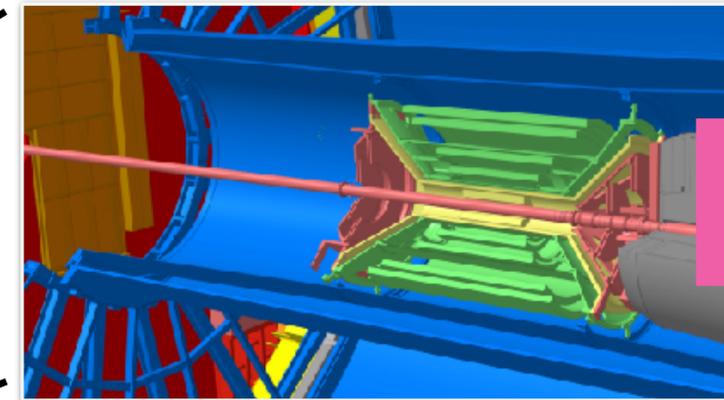


- ▶ Study of QGP in heavy-ion collisions at LHC
  - i.e. up to  $O(10k)$  particles to be tracked in a single event
- ▶ Reconstruction of charm and beauty hadrons
  - requires precise inner tracker
- ▶ Interest in low momentum ( $\approx 1$  GeV/c) particle reconstruction
  - requires low material budgets
- ▶ Moderate radiation environment ( $< 10^{14}$  1MeV  $n_{eq}/cm^2$  NIEL)



## LS2 upgrades with Monolithic Active Pixel Sensors (MAPS)

### Inner Tracking System



LS2

ITS2

#### 6 layers:

- 2 hybrid silicon pixel
- 2 silicon drift
- 2 silicon strip

#### Inner-most layer:

- radial distance: 39 mm
- material:  $X/X_0 = 1.14\%$
- pitch:  $50 \times 425 \mu\text{m}^2$
- rate capability: 1 kHz

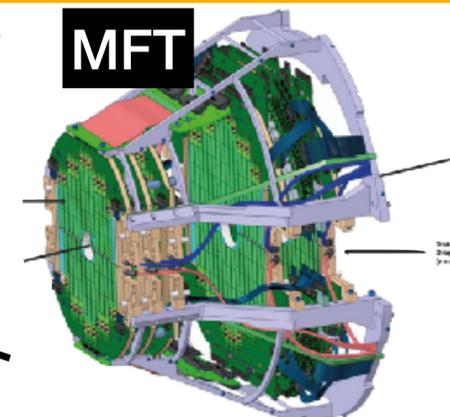
#### 7 layers:

- all MAPS
- 10 m<sup>2</sup>, 24k chips, 12.5 Giga-Pixels

#### Inner-most layer:

- radial distance: 23 mm
- material:  $X/X_0 = 0.35\%$
- pitch:  $29 \times 27 \mu\text{m}^2$
- rate capability: 100 kHz (Pb-Pb)

### Muon Forward Tracker

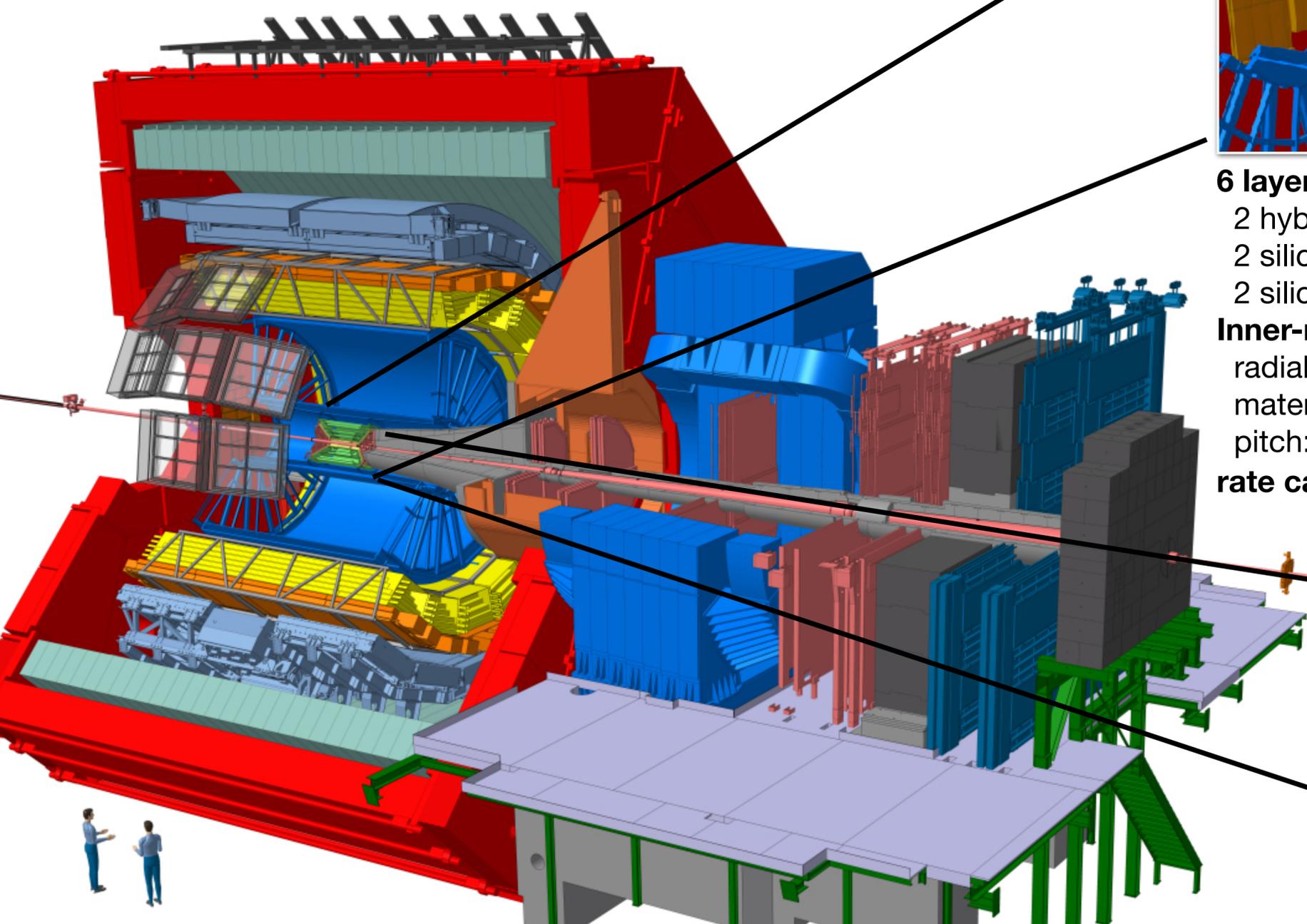


MFT

new detector

5 discs, double sided:

based on same technology as ITS2



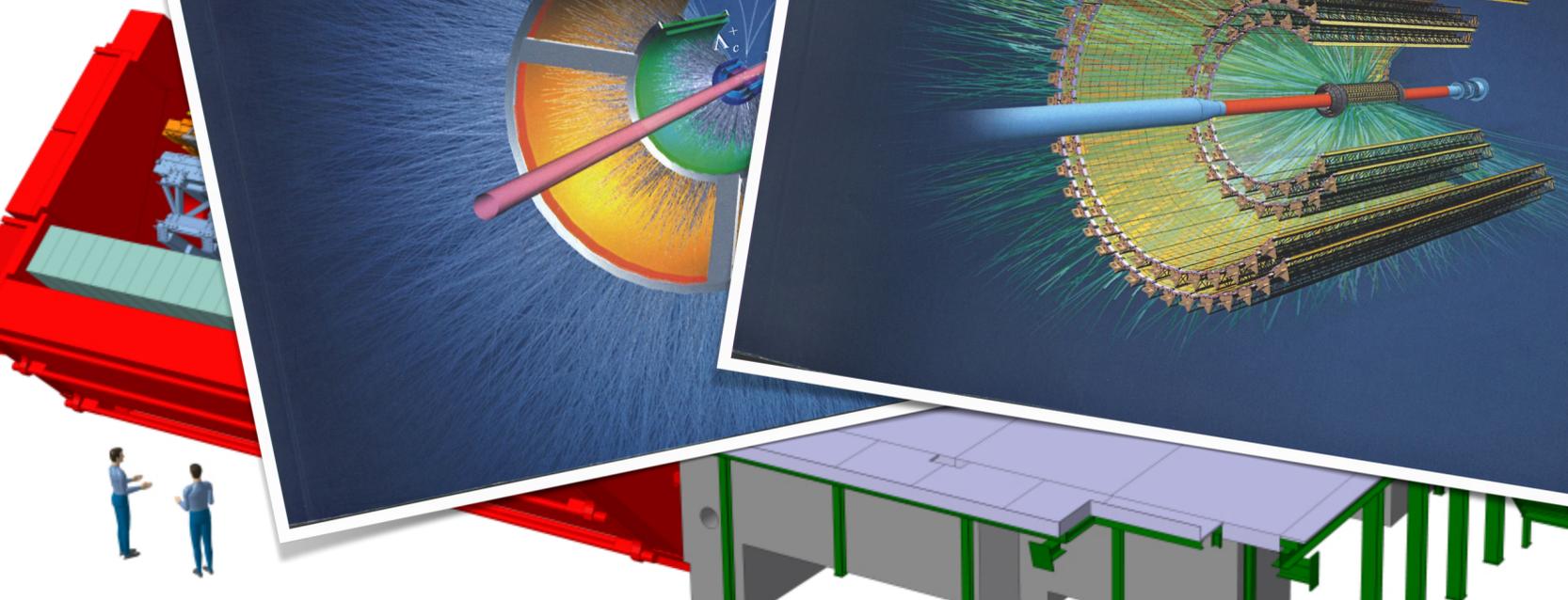
# ALICE

LS2 upgrade

Active Pixel

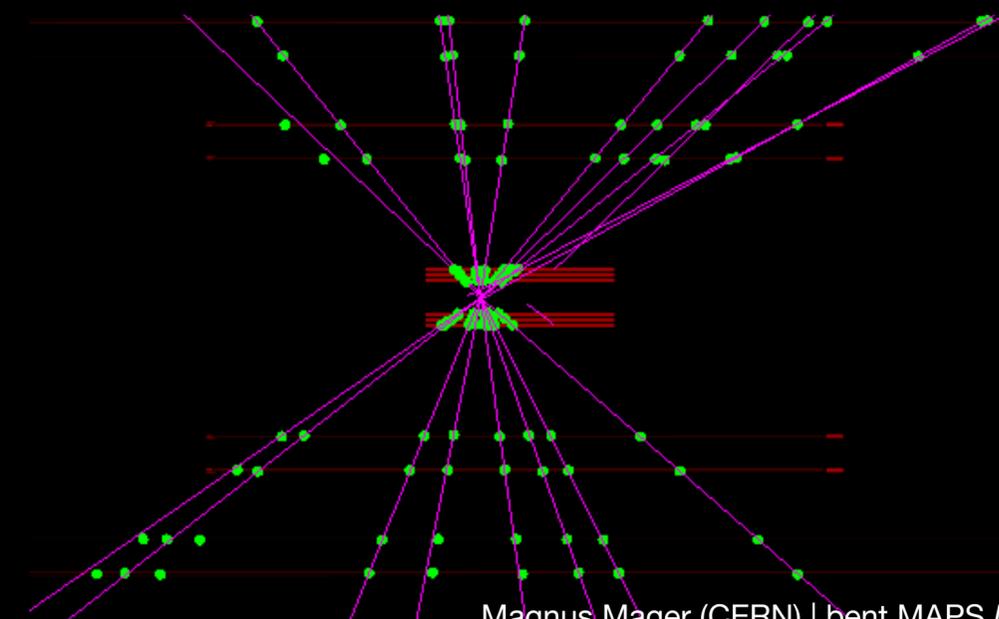
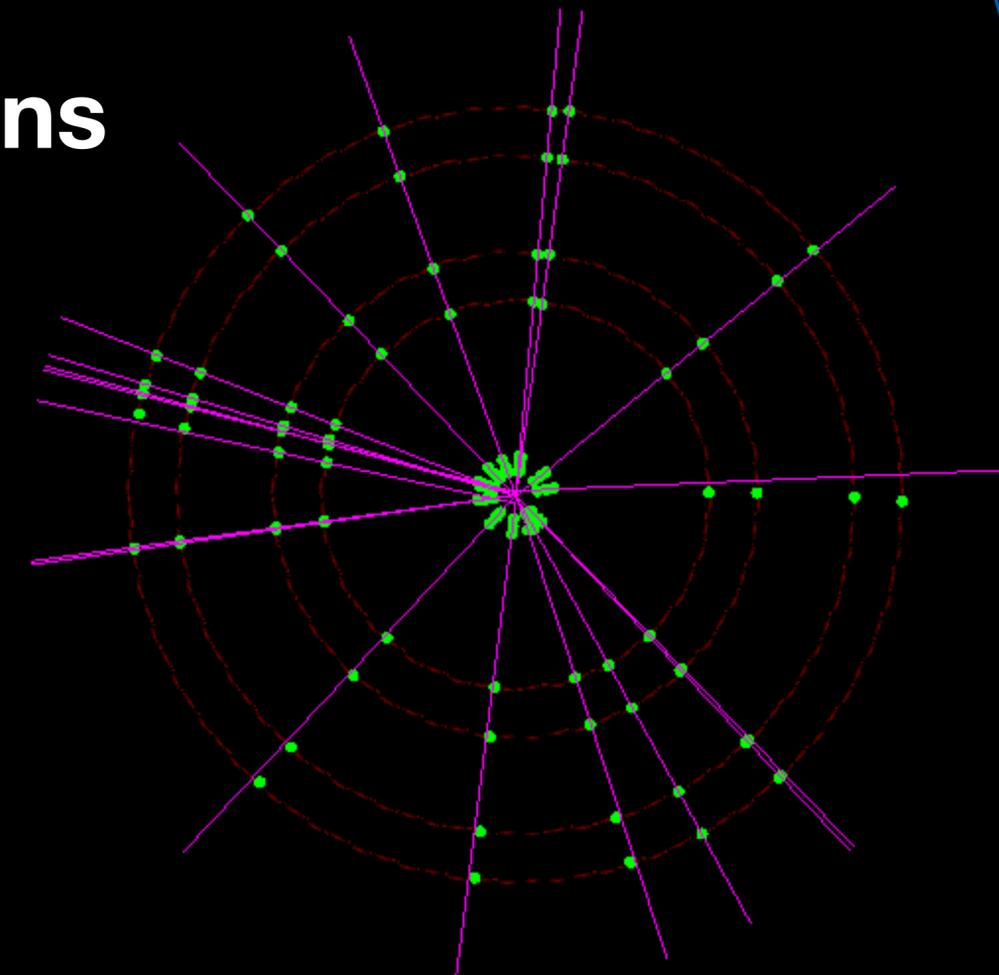
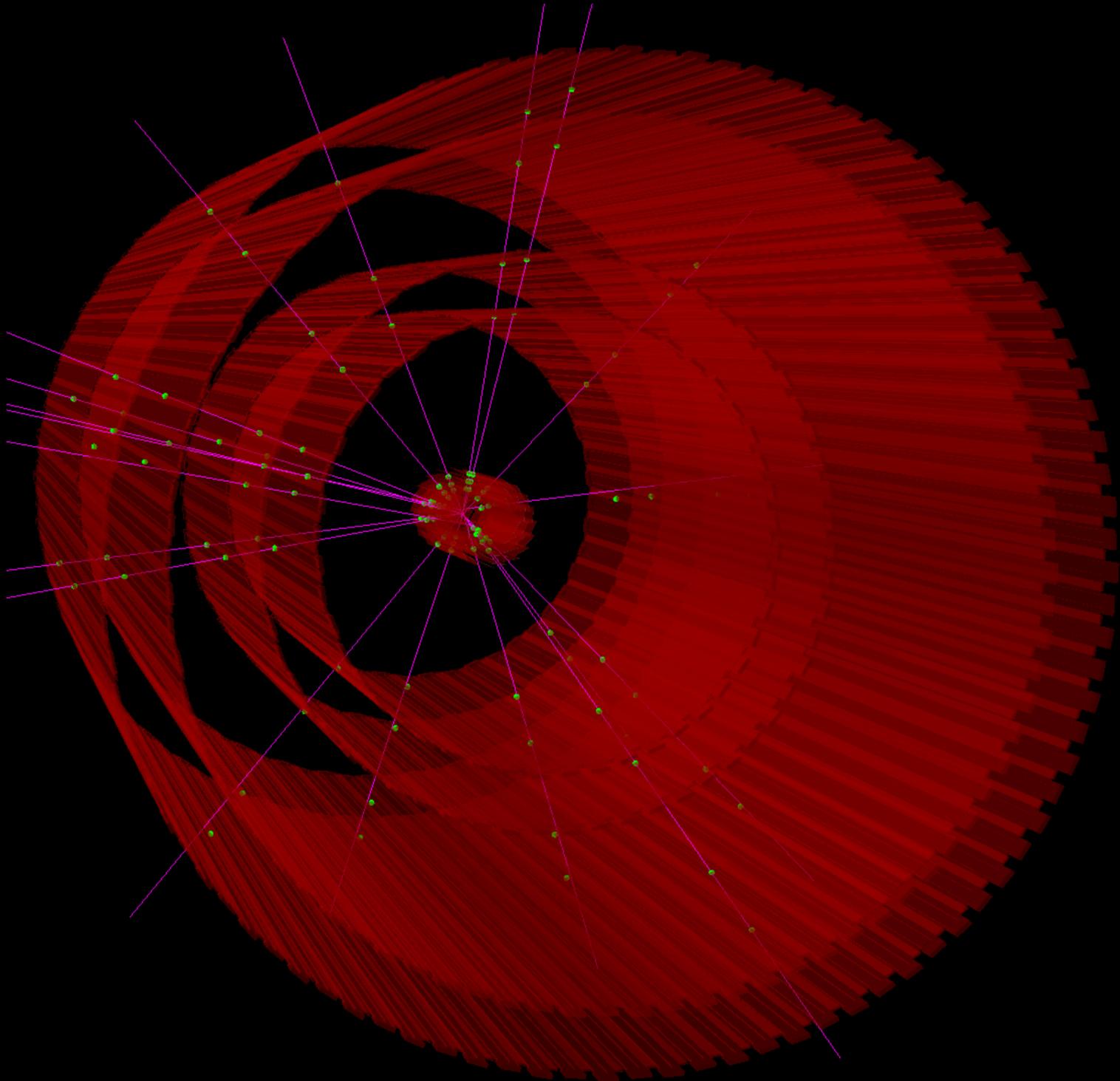


~ 10 years of R&D and C&I

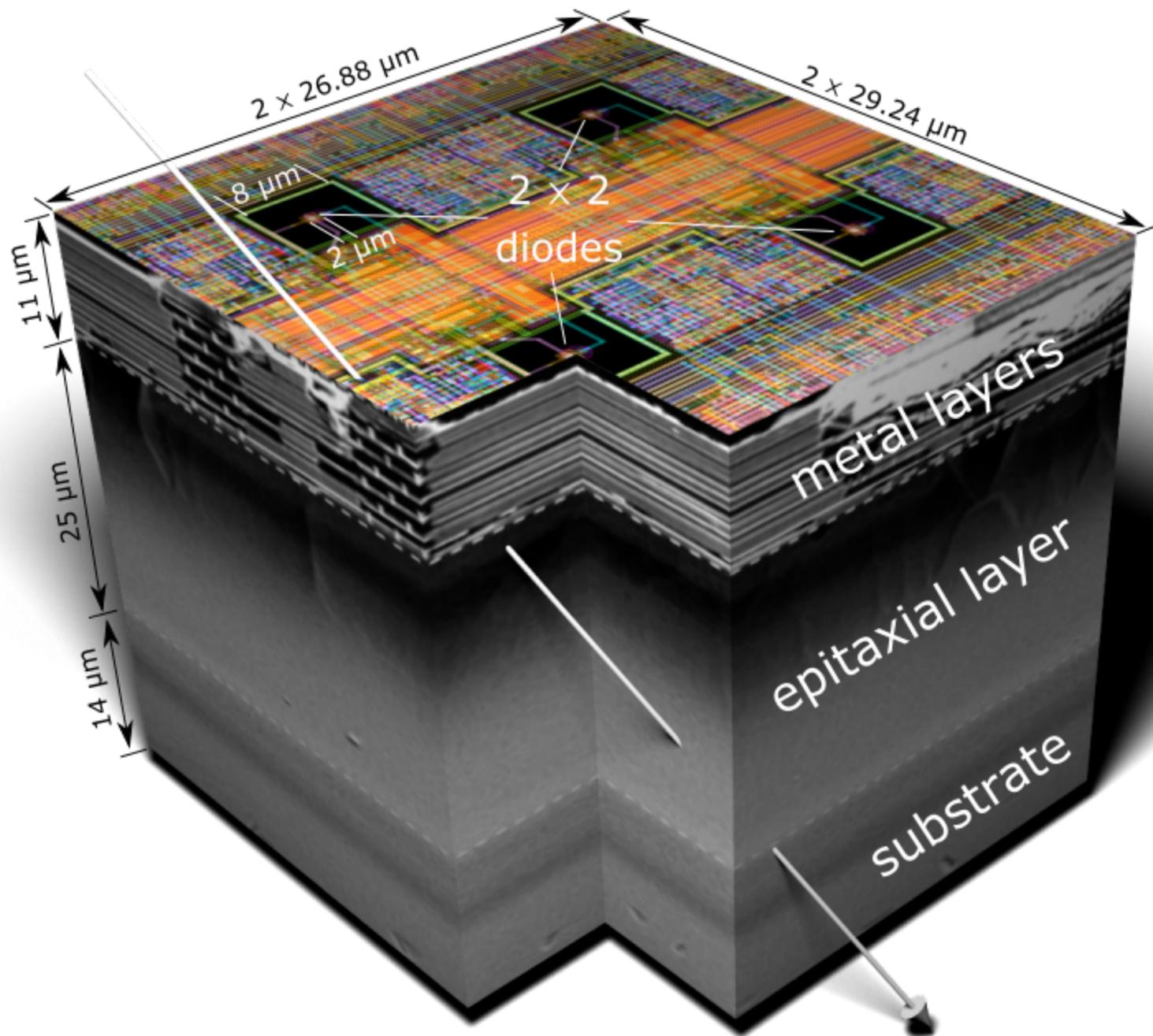


# LHC pilot beam results

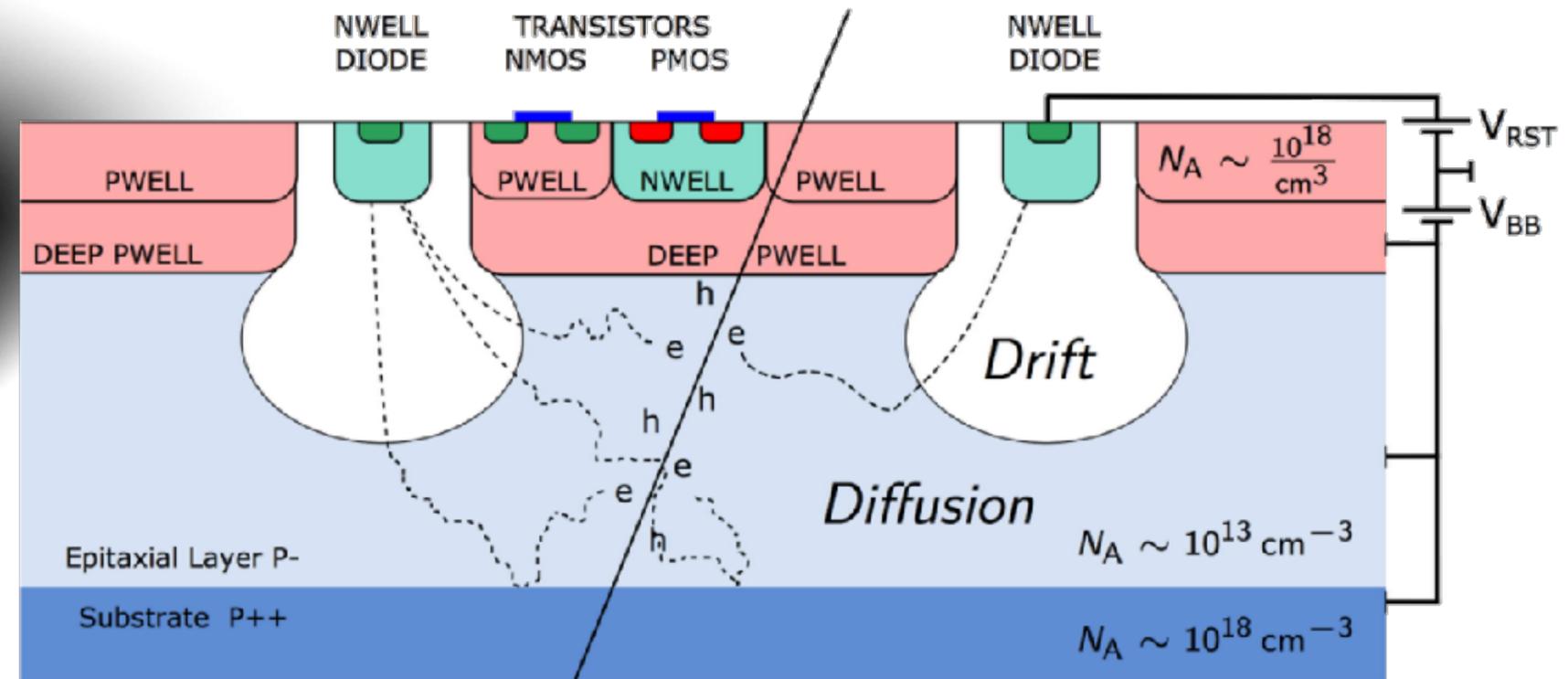
September 2021, 900 GeV proton collisions



# ALPIDE Technology

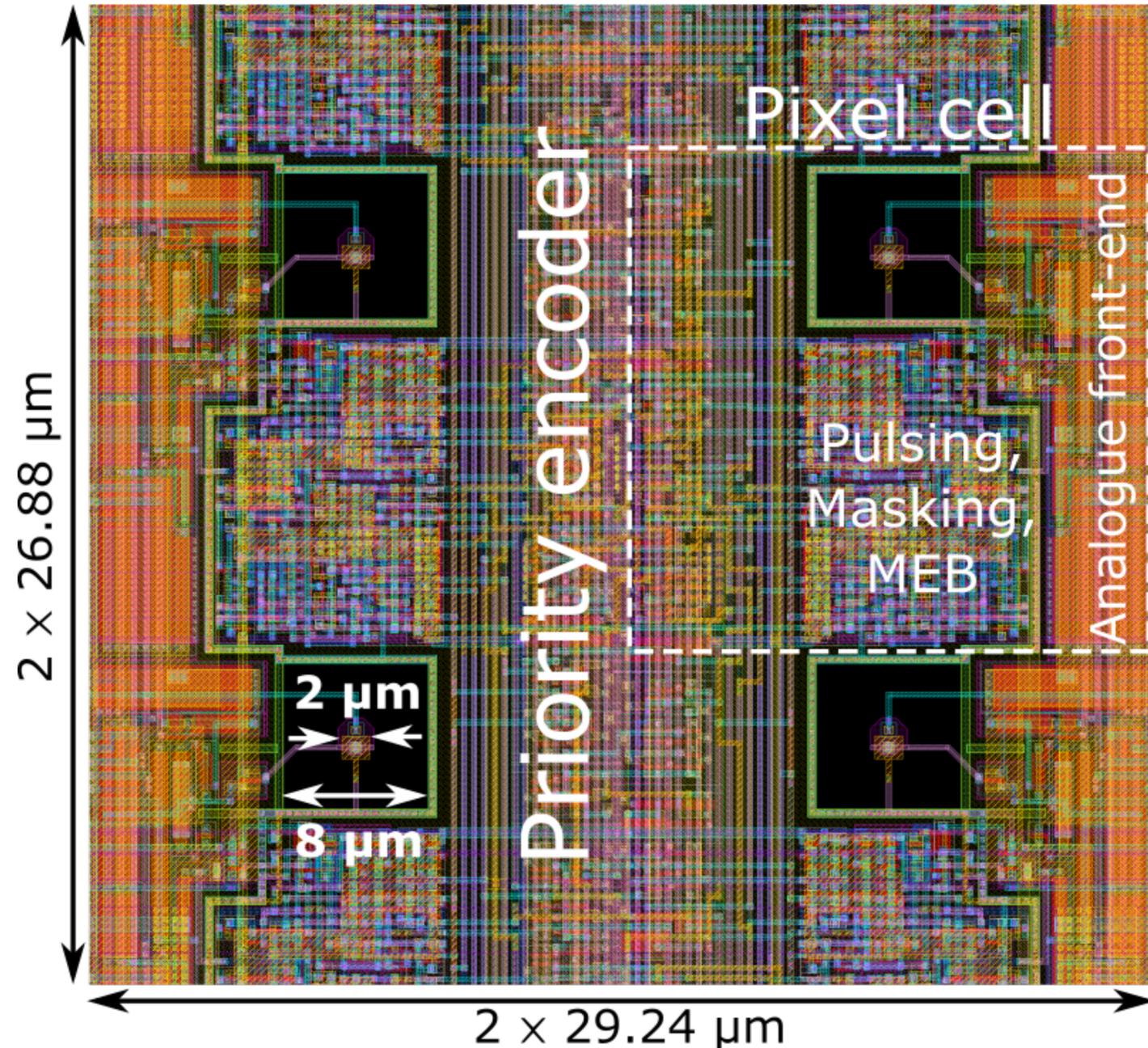


- ▶ **Process:** Tower Semiconductor 180 nm CIS
  - deep p-well to allow CMOS circuitry inside matrix
  - reverse-substrate bias
- ▶ **Detection layer:** 25 μm high-resistive (>1 kΩcm) epitaxial layer
- ▶ **Thickness:** 100 μm (OB) or 50 μm (IB)



# ALPIDE

## Pixel functionality

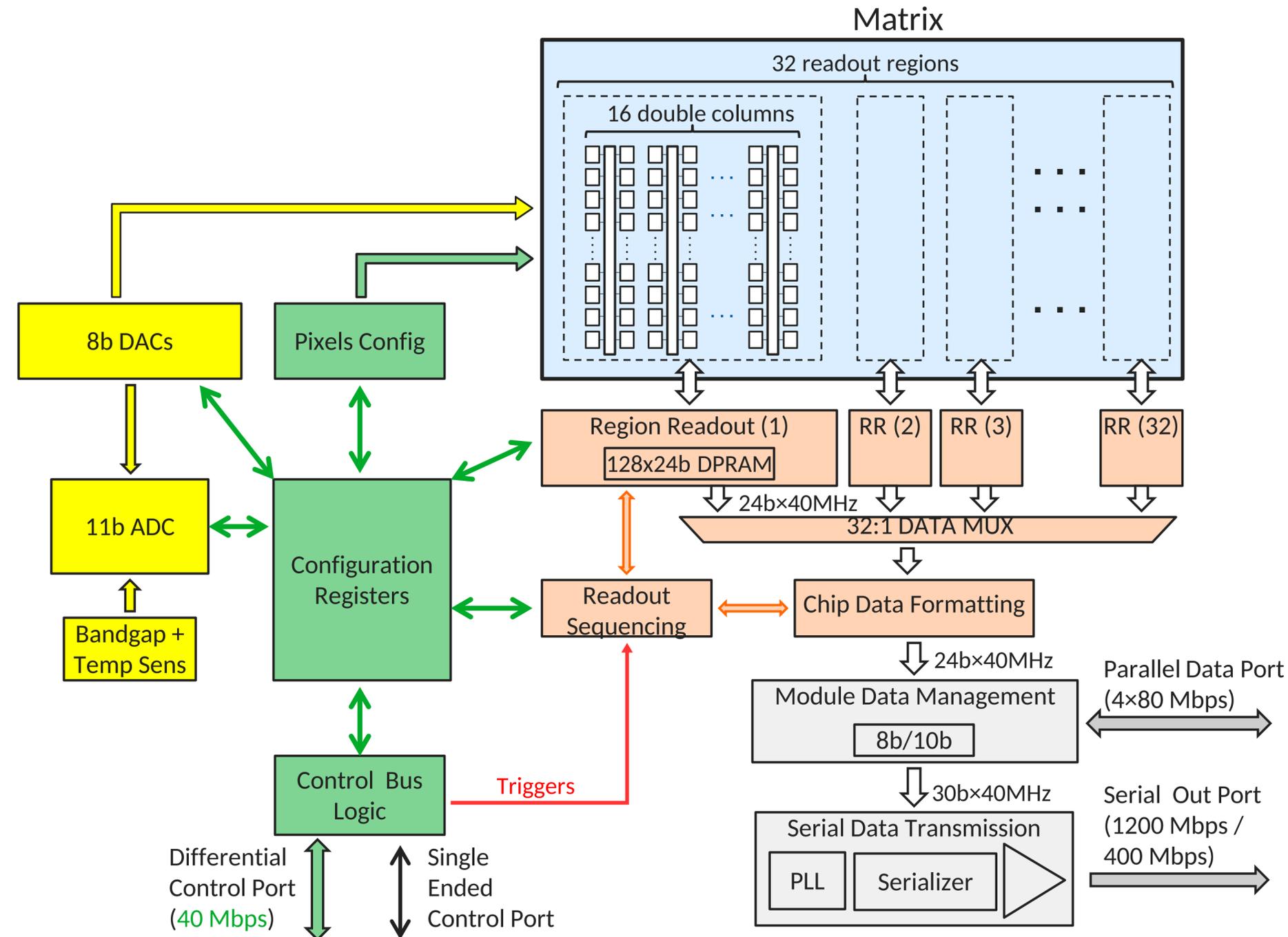


- ▶ **Front-end:** (9 transistors, full-custom)
  - continuously active
  - shaping time:  $< 10 \mu\text{s}$
  - power consumption: 40 nW
- ▶ **Multiple-event memory:** 3 stages (62 transistors, full-custom)
- ▶ **Configuration:** pulsing & masking registers (31 transistors, full-custom)
- ▶ **Testing:** analogue and digital test pulse circuitry (17 transistors, full-custom)
- ▶ **Readout:** priority encoder, asynchronous, hit-driven

**O(200) transistors / pixel (wrt. 3T/4T)**

# ALPIDE

## Global architecture



- ▶ **Fully integrated:**
  - next active circuit  $\approx 8$  m away off-detector
- ▶ **Strobing:**
  - global shutter
  - either triggered or in continuous sequence
- ▶ **Data interface:**
  - high-speed serial link using copper cables

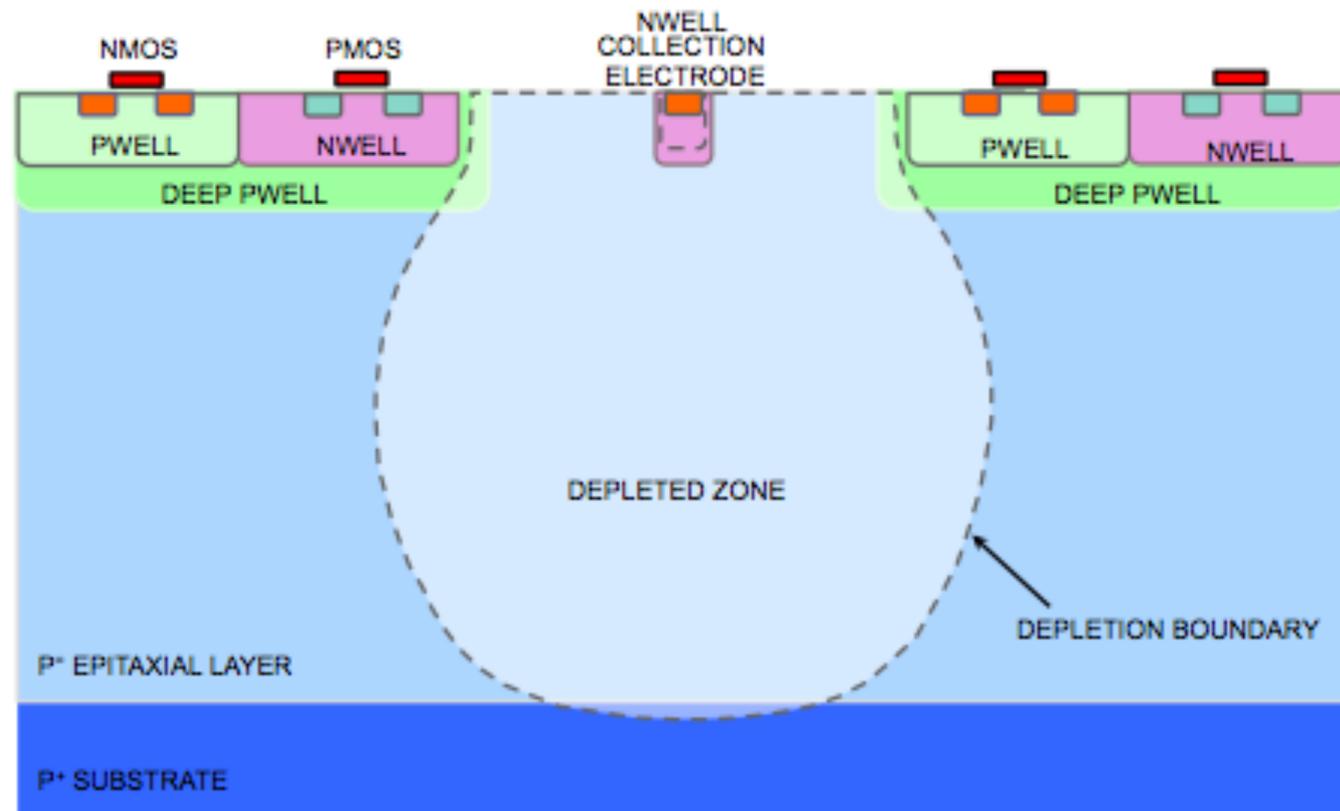
**MAPS are highly integrated devices: reducing material budget + integration complexity**

# Process modification

## Fully depleted MAPS – ITS2 “side project”

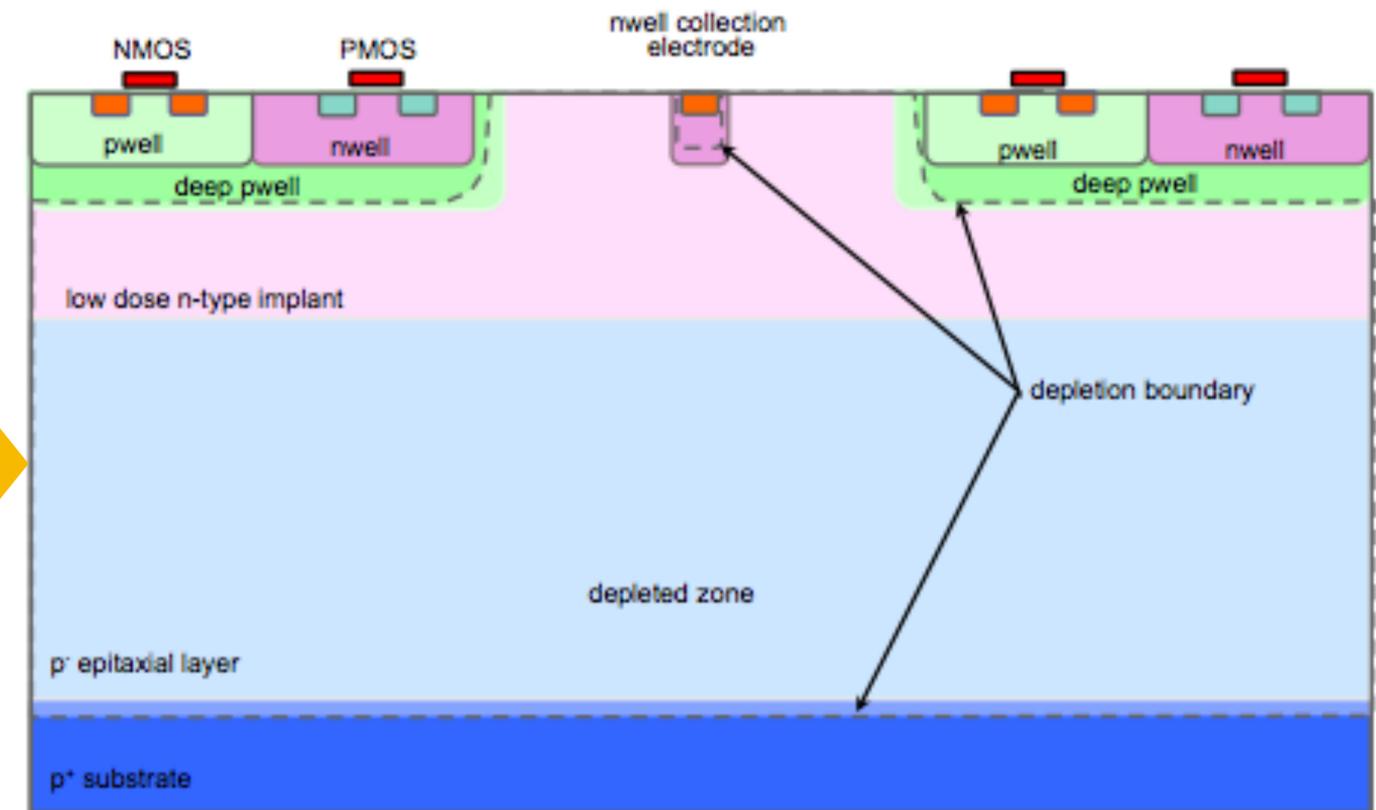


Foundry standard process



Developed and prototyped within ALPIDE R&D

Modified process CERN/Tower



Partially depleted epitaxial layer  
Charge collection time < 30 ns  
Operational up to  $10^{14}$  1 MeV  $n_{eq}/cm^2$

Fully depleted epitaxial layer  
Charge collection time < 1 ns  
Operational up to  $10^{15}$  1 MeV  $n_{eq}/cm^2$

**Excellent co-operation with foundry!**

Now being further pursued with MALTA, CLICpix, FastPix, ...

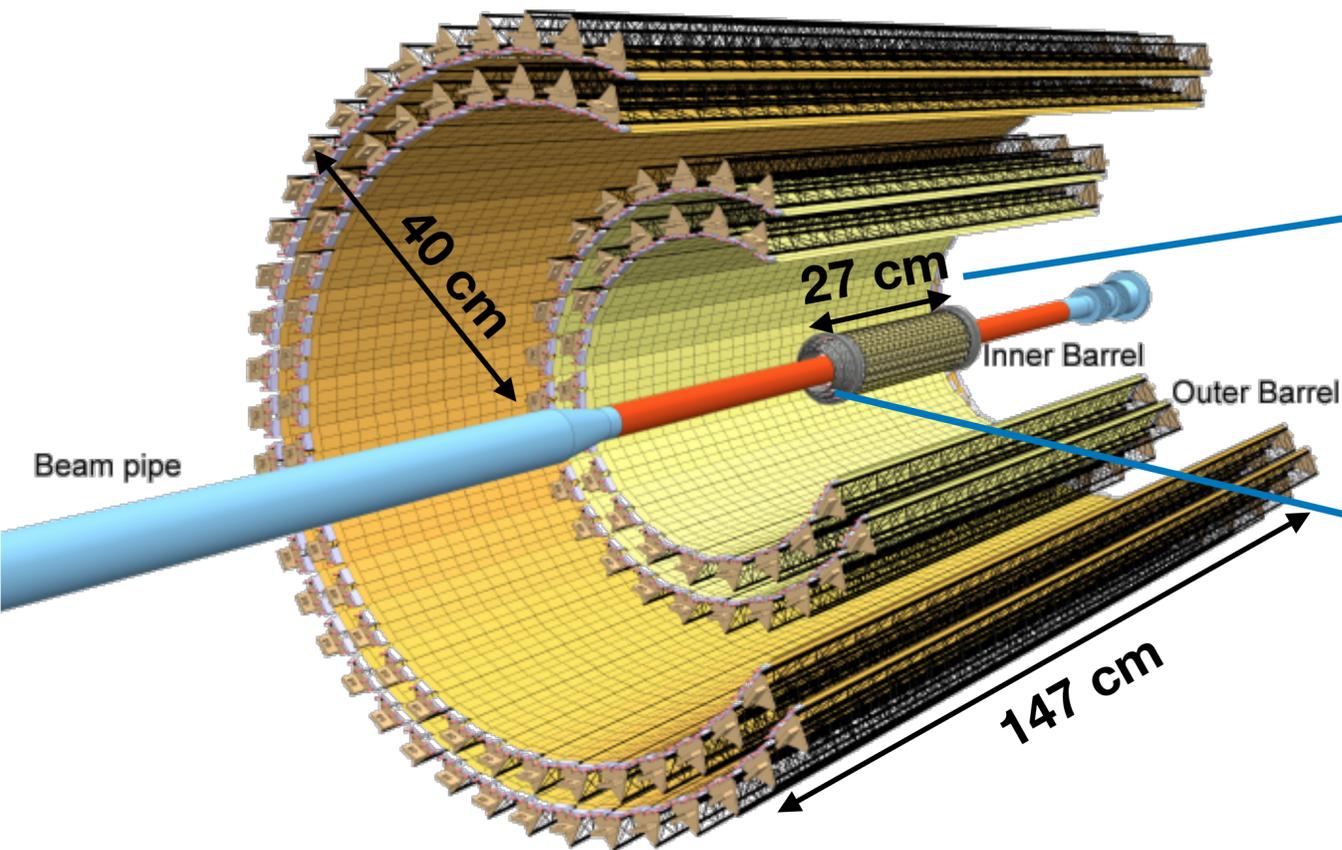
More details:

NIM A871 (2017) 90-96

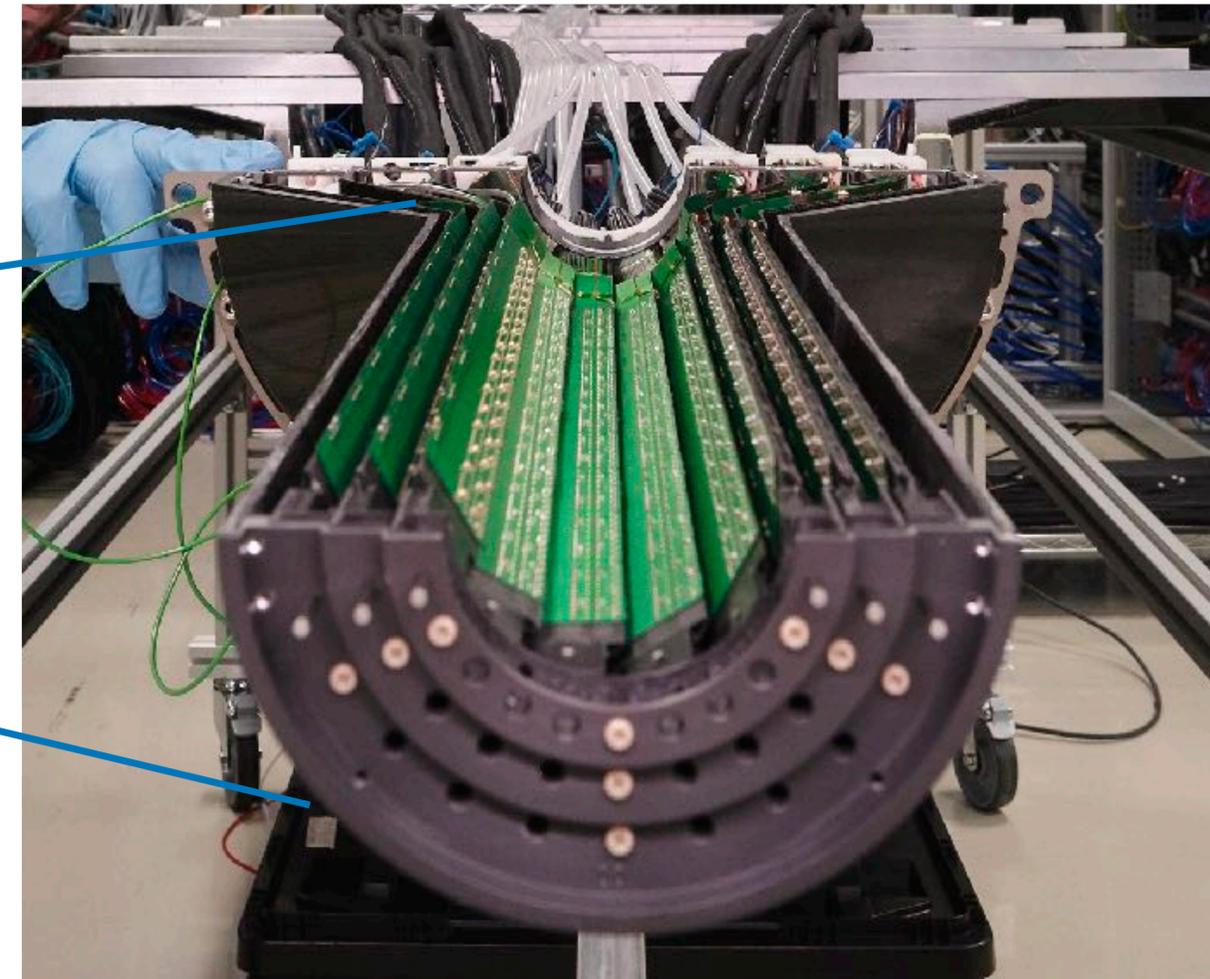
<https://doi.org/10.1016/j.nima.2017.07.046>

# ITS2 inner barrel

Layout



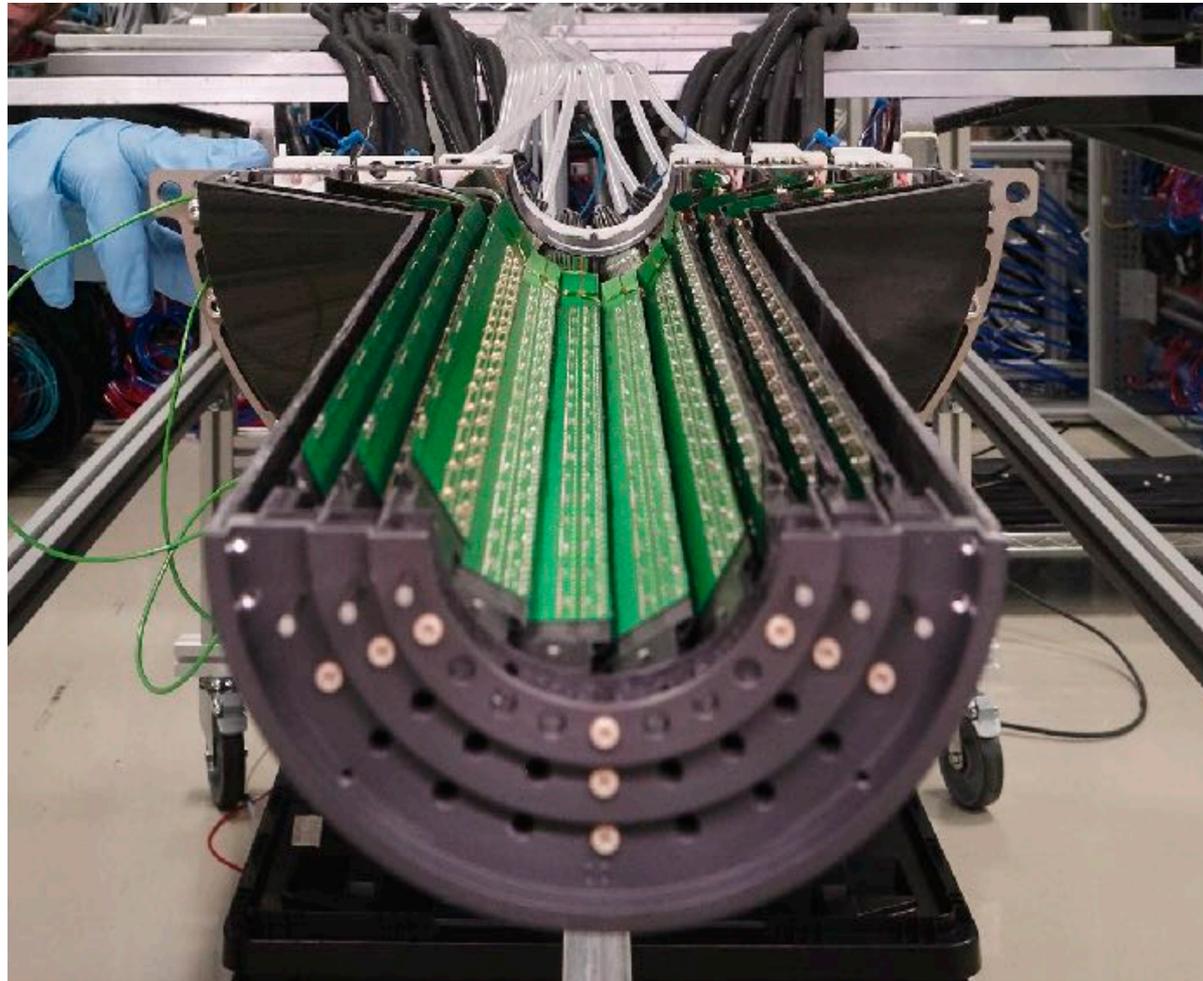
ITS2: assembled three inner-most half-layers



- ▶ ITS2 is expected to perform according to specifications or even better
- ▶ The Inner Barrel is ultra-light but rather packed → further improvements seem possible
- ▶ **Key questions: Can we get closer to the IP? Can we reduce the material further?**

# ITS2 → ITS3

idea



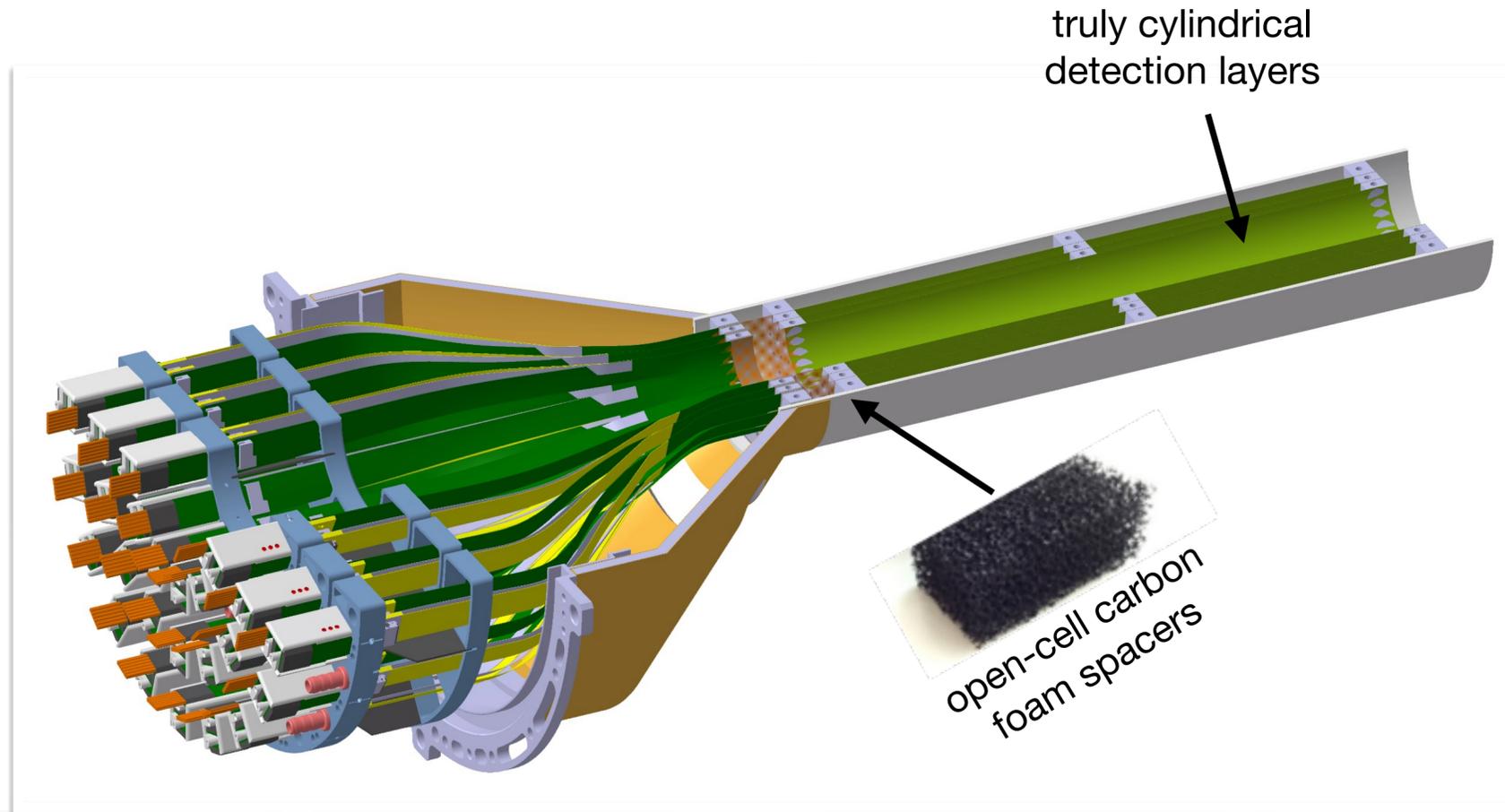
▶ By employing wafer-scale, bent sensors it can be improved on:

- material budget (~ factor 7)
- distance to interaction point (no “turbo” geometry)

**ITS3 Letter of Intent**  
**[CERN-LHCC-2019-018 ; LHCC-I-034]**

**The idea is simple, but requires quite some R&D — which we started in Dec 2019!**

# ITS3 detector concept



## ▶ Key ingredients:

- 300 mm wafer-scale sensors, fabricated using stitching
- thinned down to 20-40  $\mu\text{m}$  (0.02-0.04%  $X_0$ ), making them flexible
- bent to the target radii
- mechanically held in place by carbon foam ribs

## ▶ Key benefits:

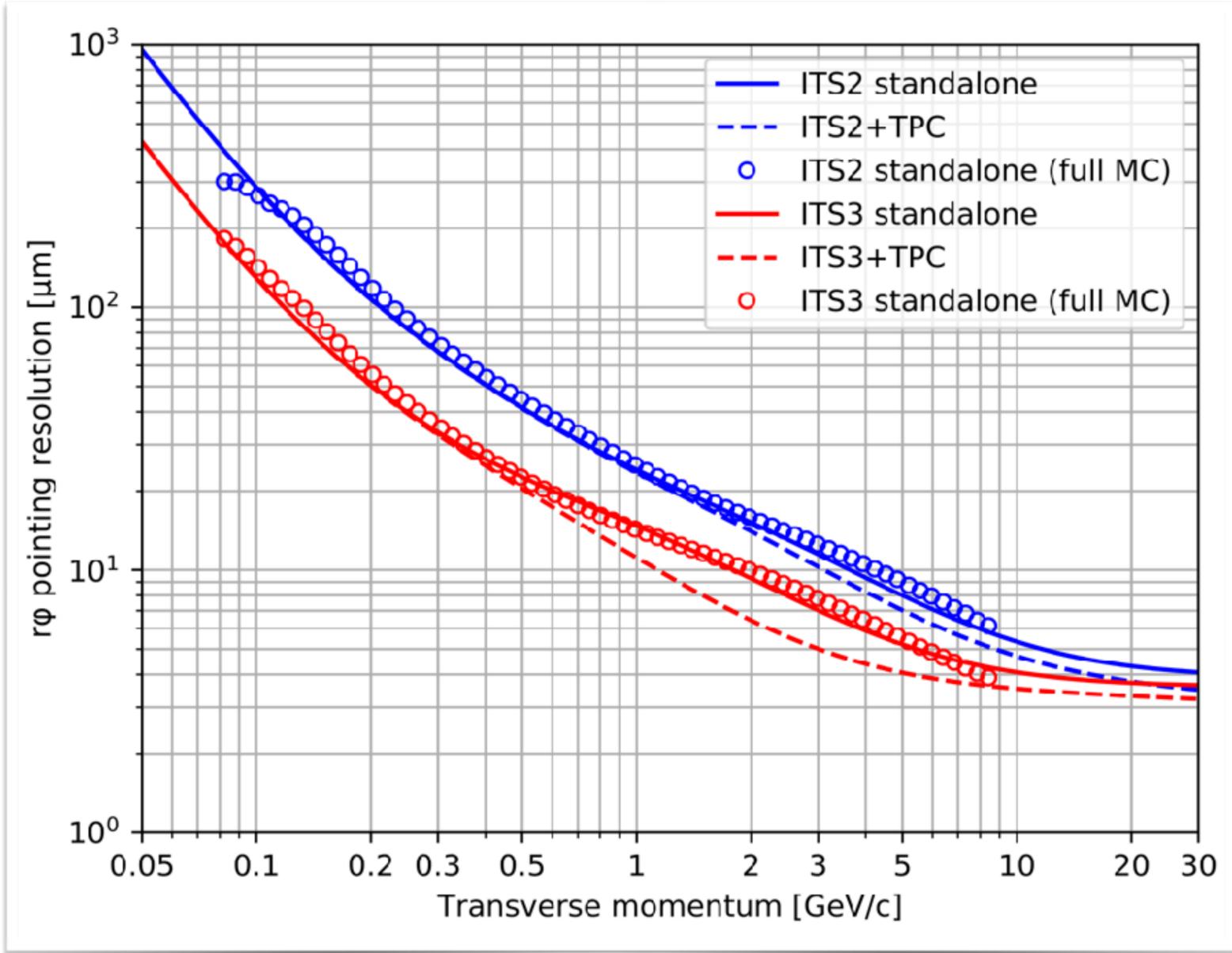
- extremely low material budget: 0.02-0.04%  $X_0$  (beampipe: 500  $\mu\text{m}$  Be: 0.14%  $X_0$ )
- homogeneous material distribution: negligible systematic error from material distribution

Beam pipe Inner/Outer Radius (mm)	16.0/16.5		
IB Layer Parameters	Layer 0	Layer 1	Layer 2
Radial position (mm)	18.0	24.0	30.0
Length (sensitive area) (mm)	300		
Pseudo-rapidity coverage	$\pm 2.5$	$\pm 2.3$	$\pm 2.0$
Active area (cm <sup>2</sup> )	610	816	1016
Pixel sensor dimensions (mm <sup>2</sup> )	280 x 56.5	280 x 75.5	280 x 94
Number of sensors per layer	2		
Pixel size ( $\mu\text{m}^2$ )	0 (10 x 10)		

**The whole detector will consist of six (!) sensors (current ITS IB: 432) – and barely anything else**

# ITS3 performance figures

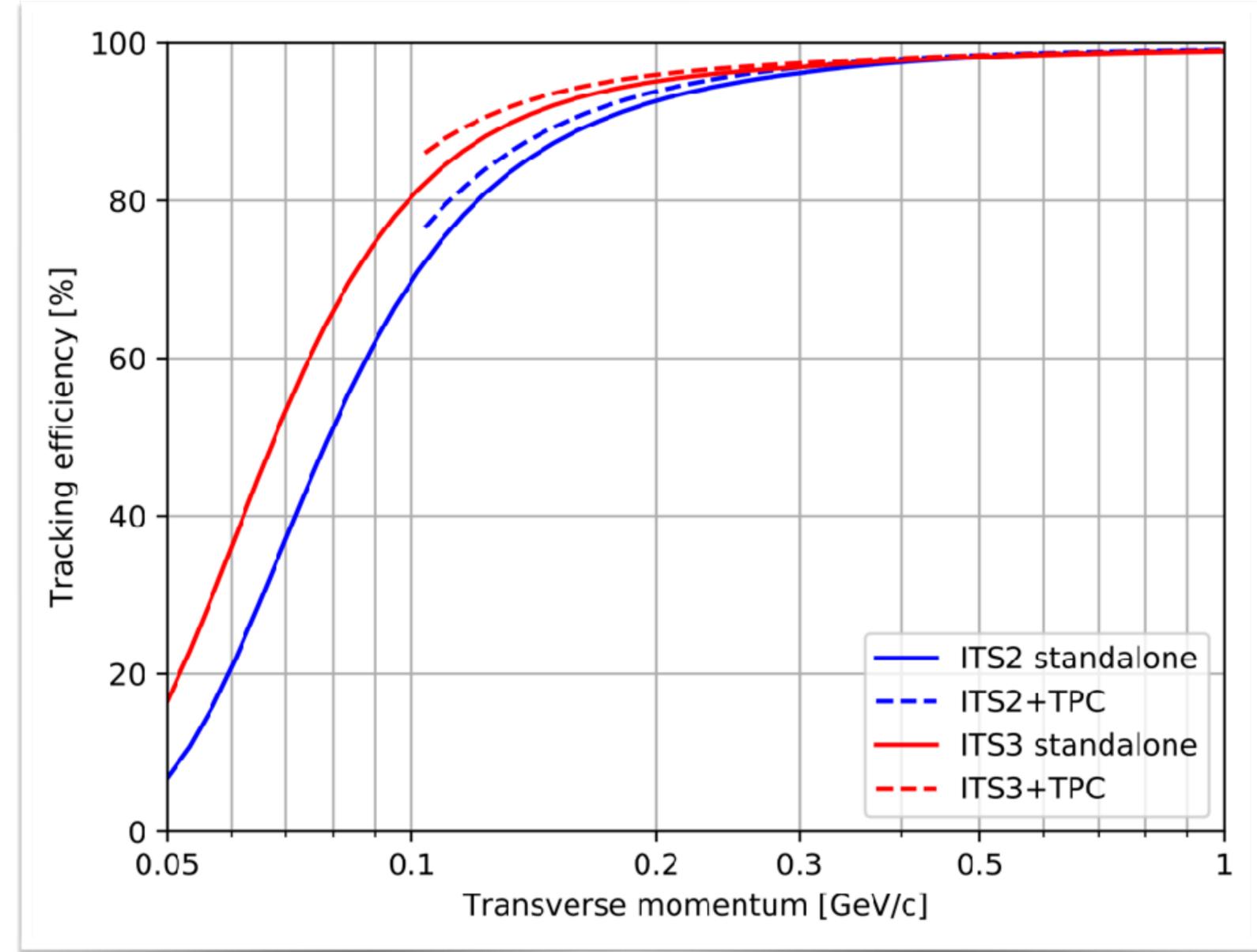
pointing resolution



[ALICE-PUBLIC-2018-013]

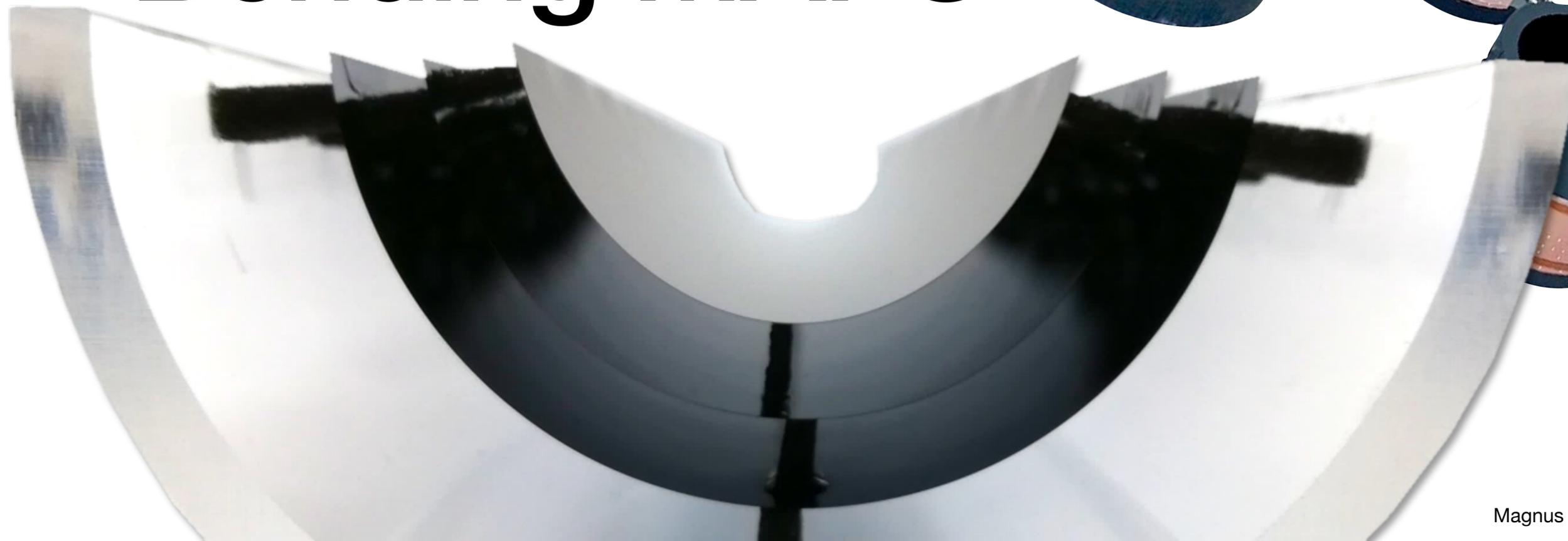
improvement of factor 2 over all momenta

tracking efficiency



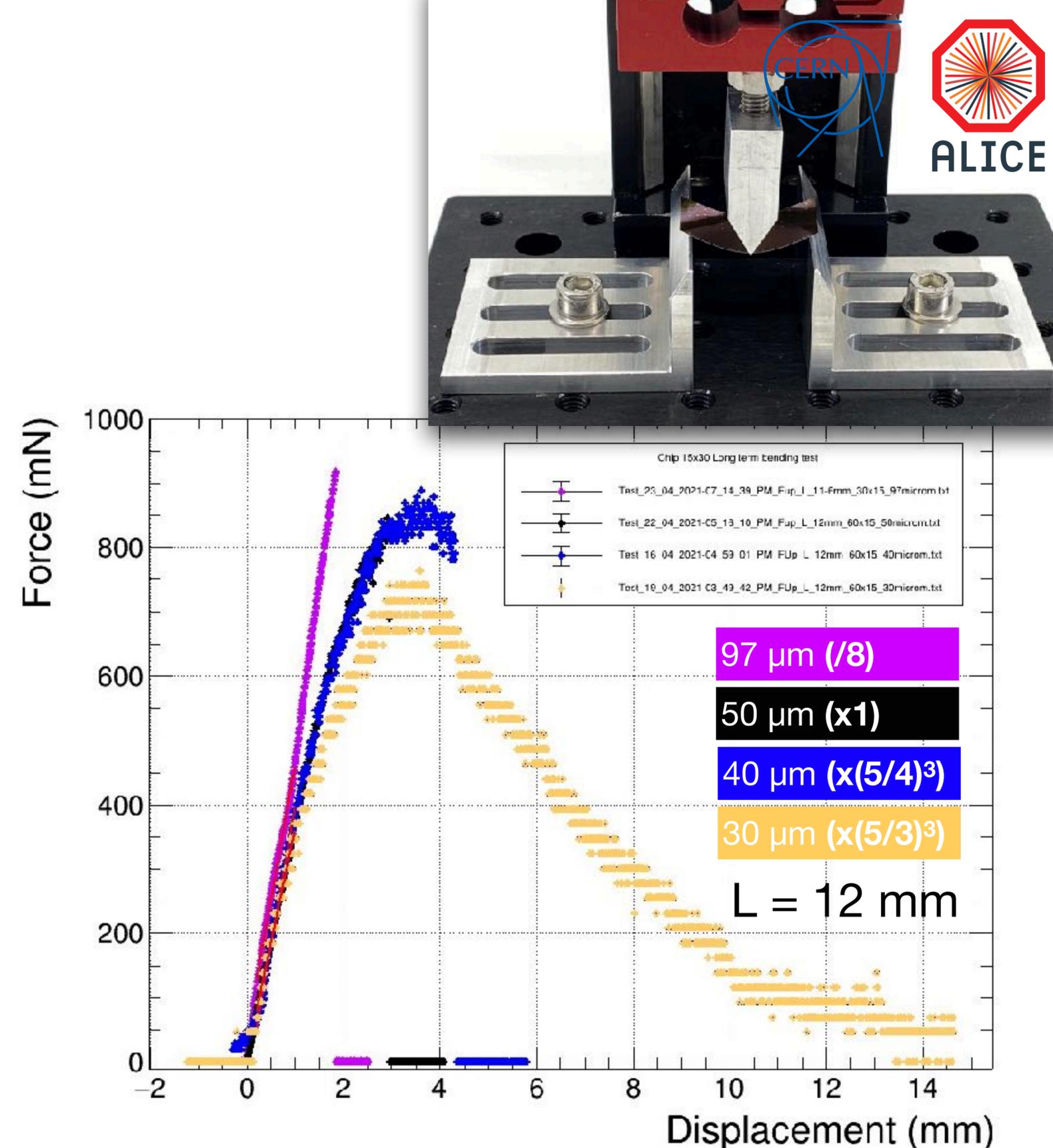
large improvement for low transverse momenta

# Bending MAPS

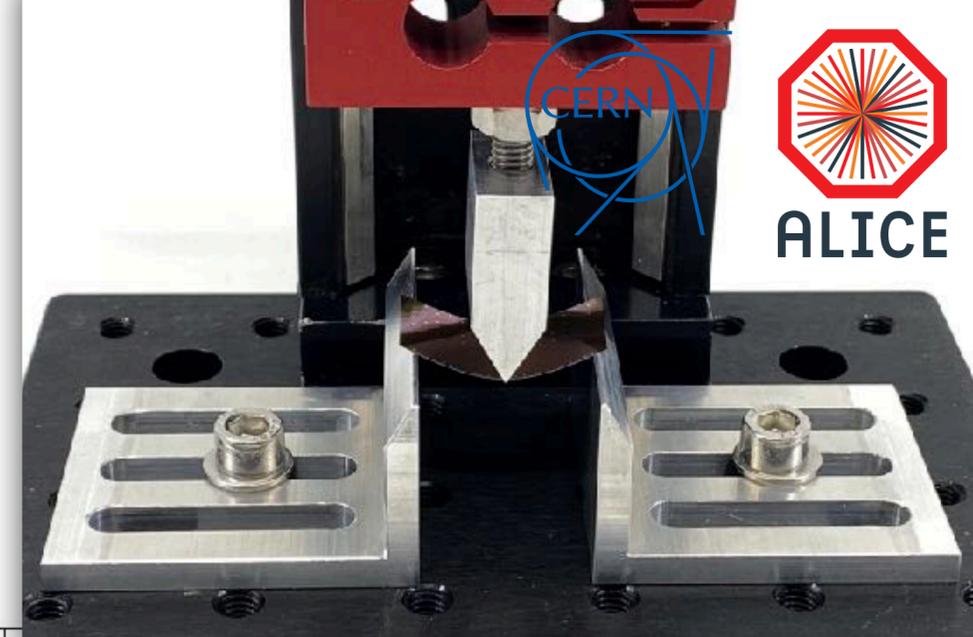


# Flexibility of silicon

- ▶ **Monolithic Active Pixel Sensors** are quite flexible
  - already at thicknesses that are used for current detectors
- ▶ Bending force scales as  $(\text{thickness})^{-3}$ 
  - large benefit from thinner sensors
- ▶ Breakage at smaller radii for thinner chips
  - again benefit from thinner sensors
- ▶ **Our target values are very feasible!**

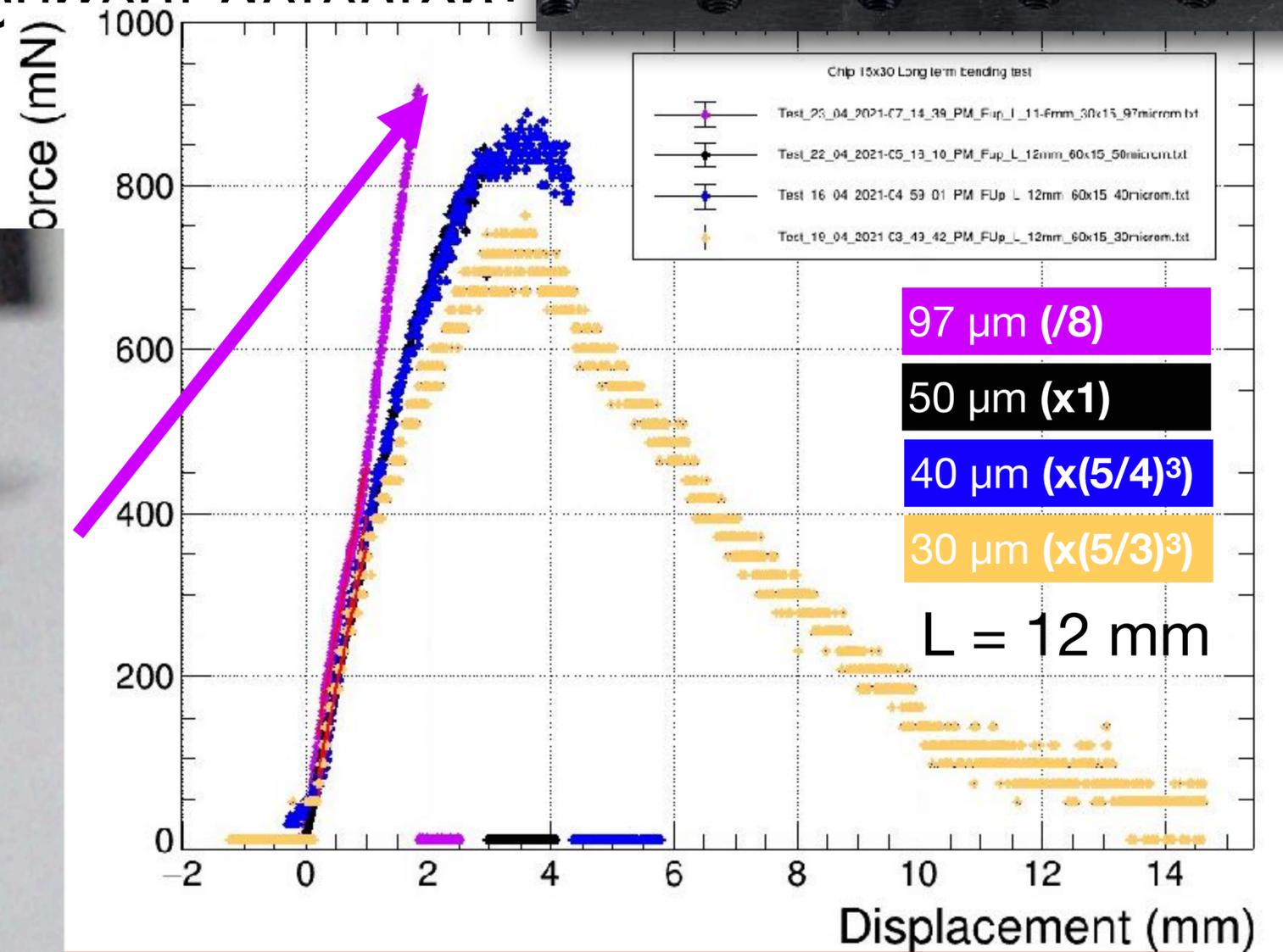
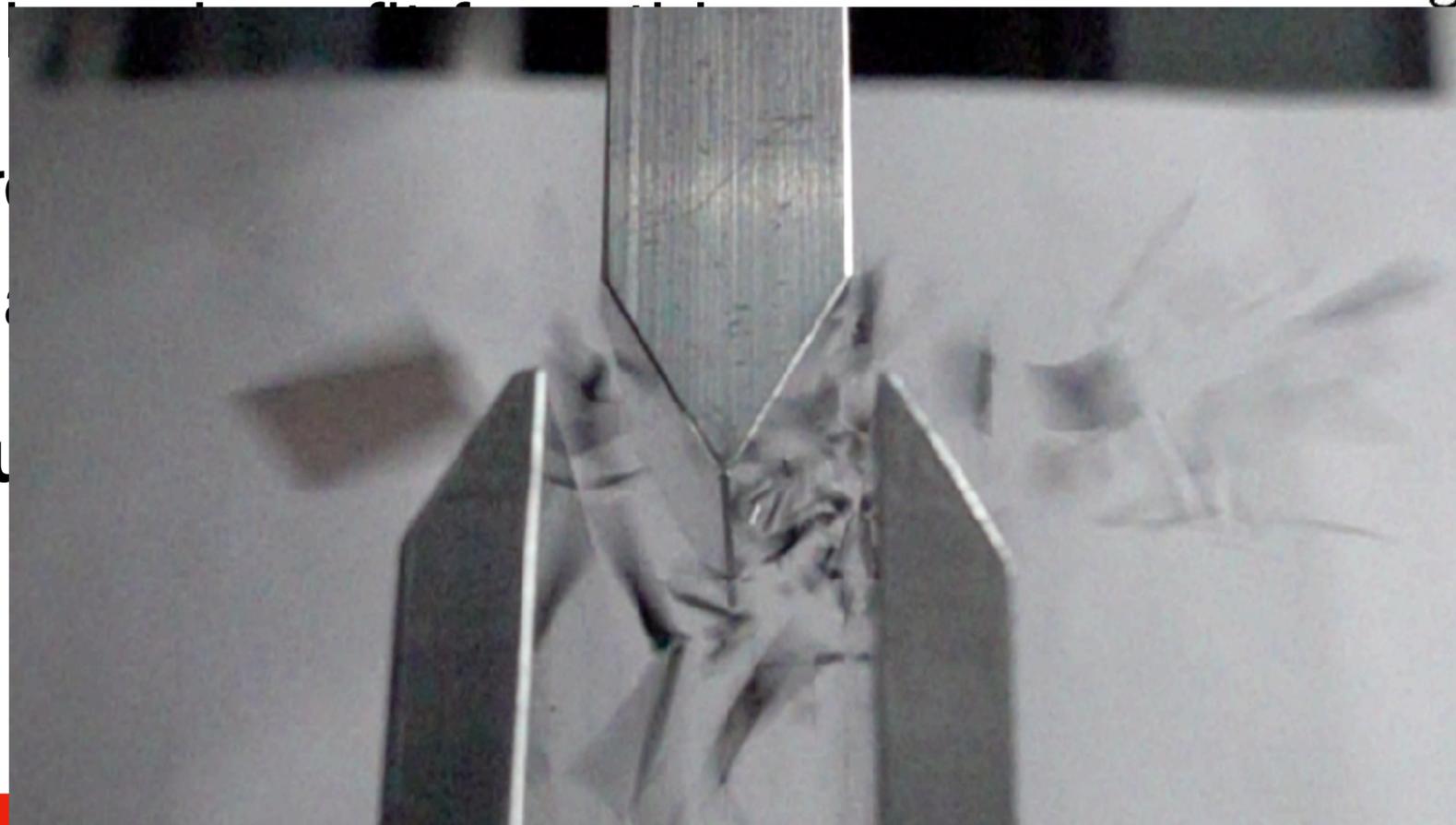


# Flexibility of silicon



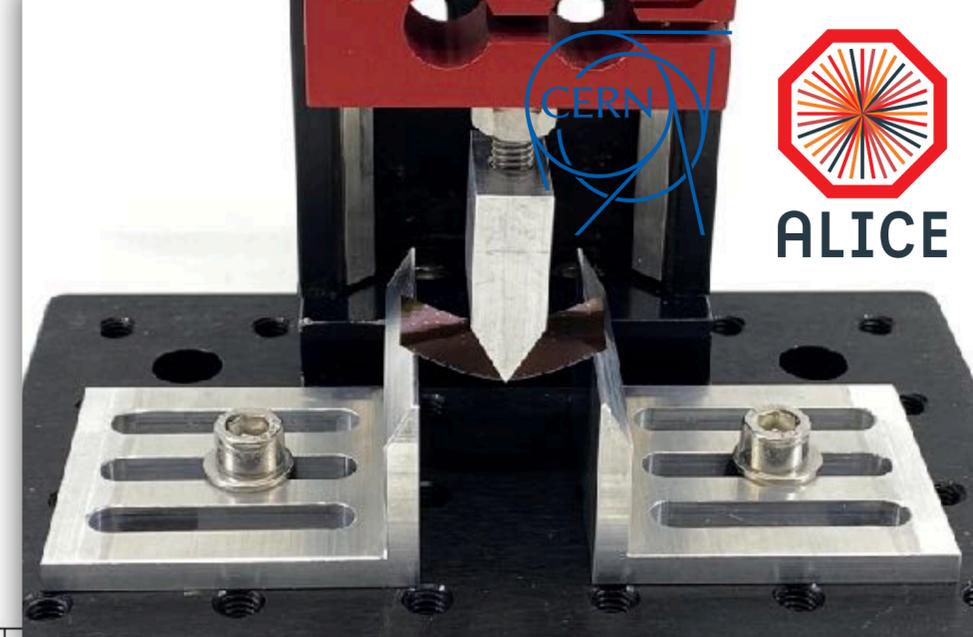
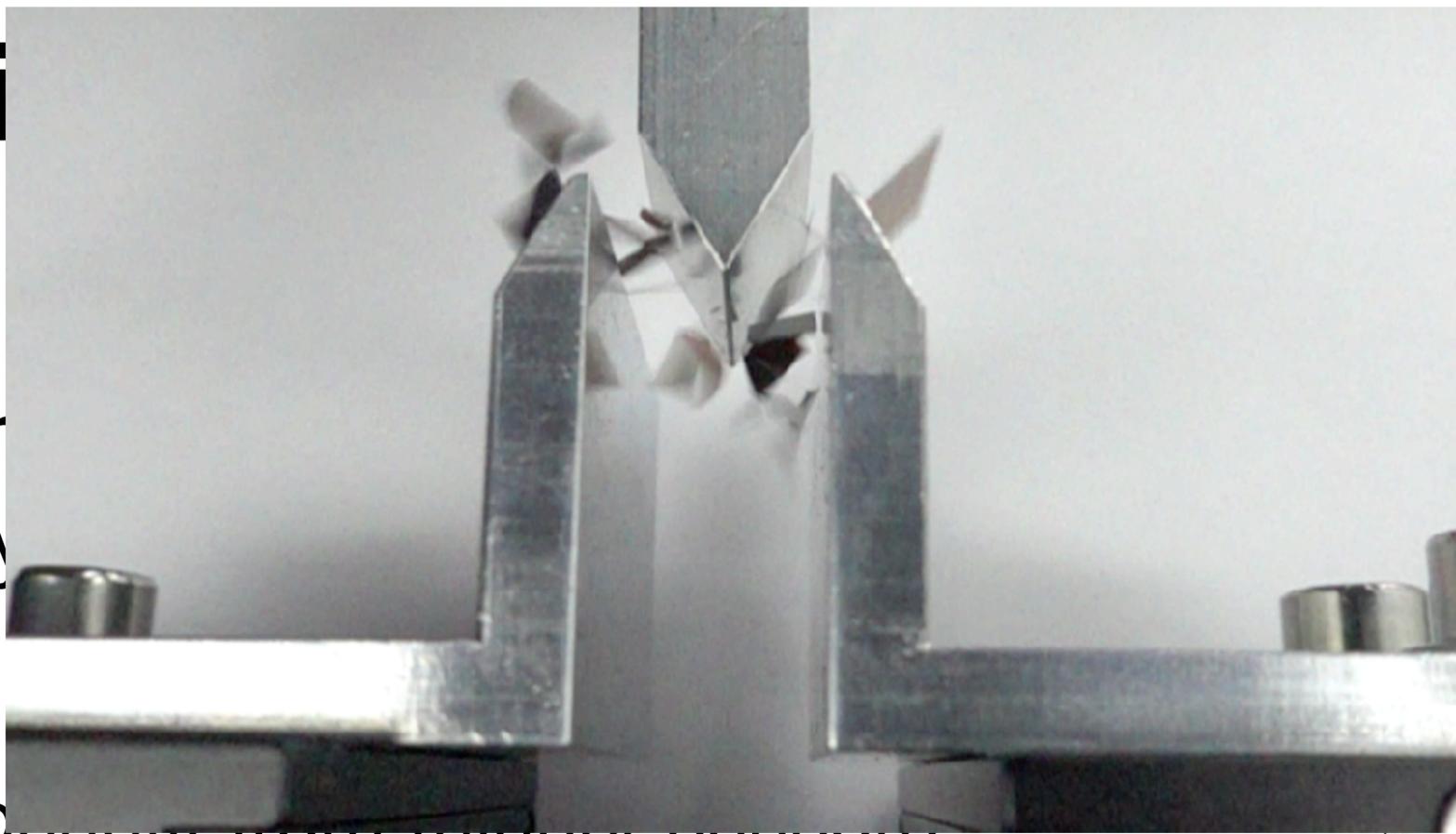
- ▶ **Monolithic Active Pixel Sensors** are quite flexible
  - already at thicknesses that are used for current detectors

- ▶ Bending force scales as  $(\text{thickness})^{-3}$

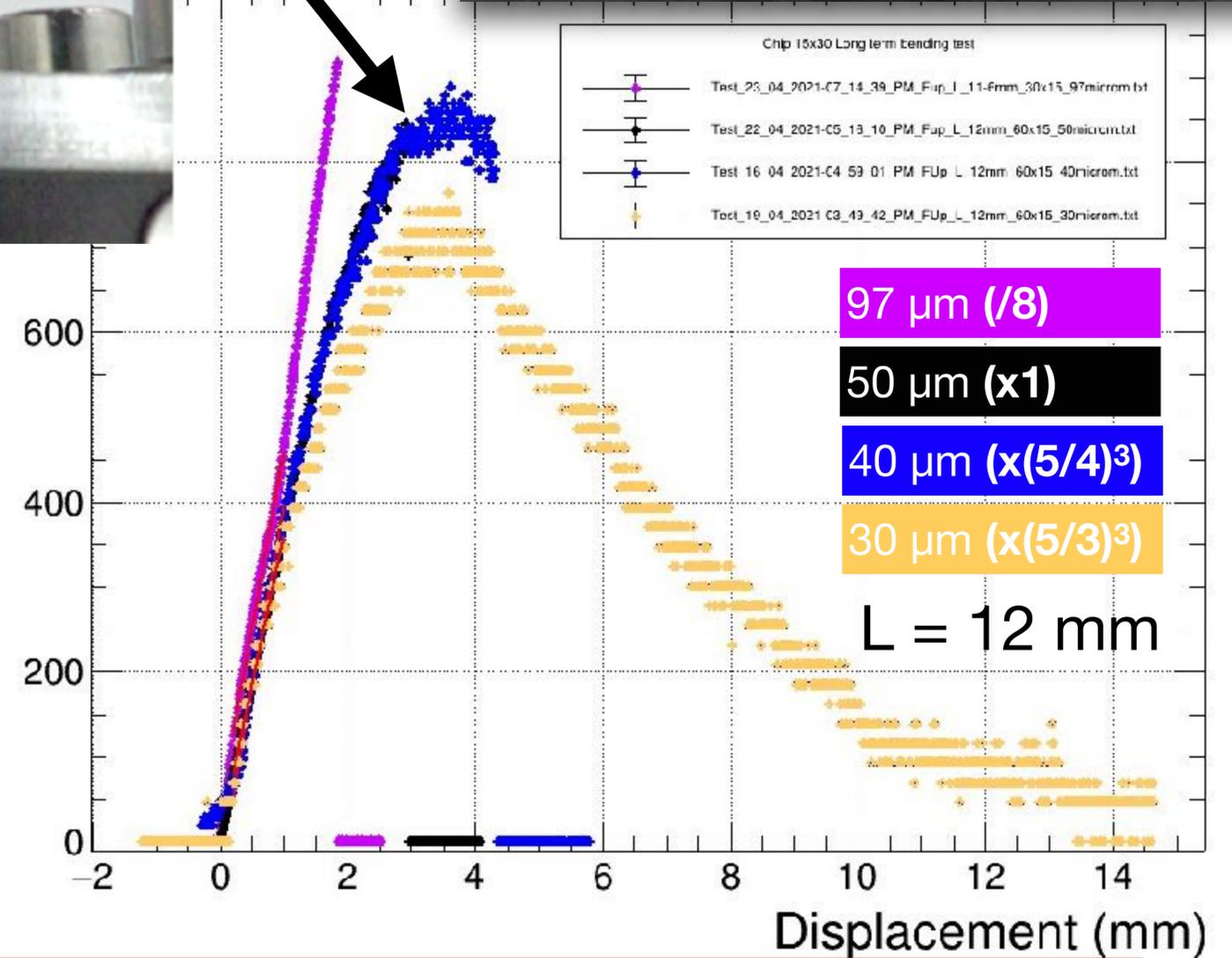


There is quite some margin already at 50  $\mu\text{m}$ !

# Flexibi



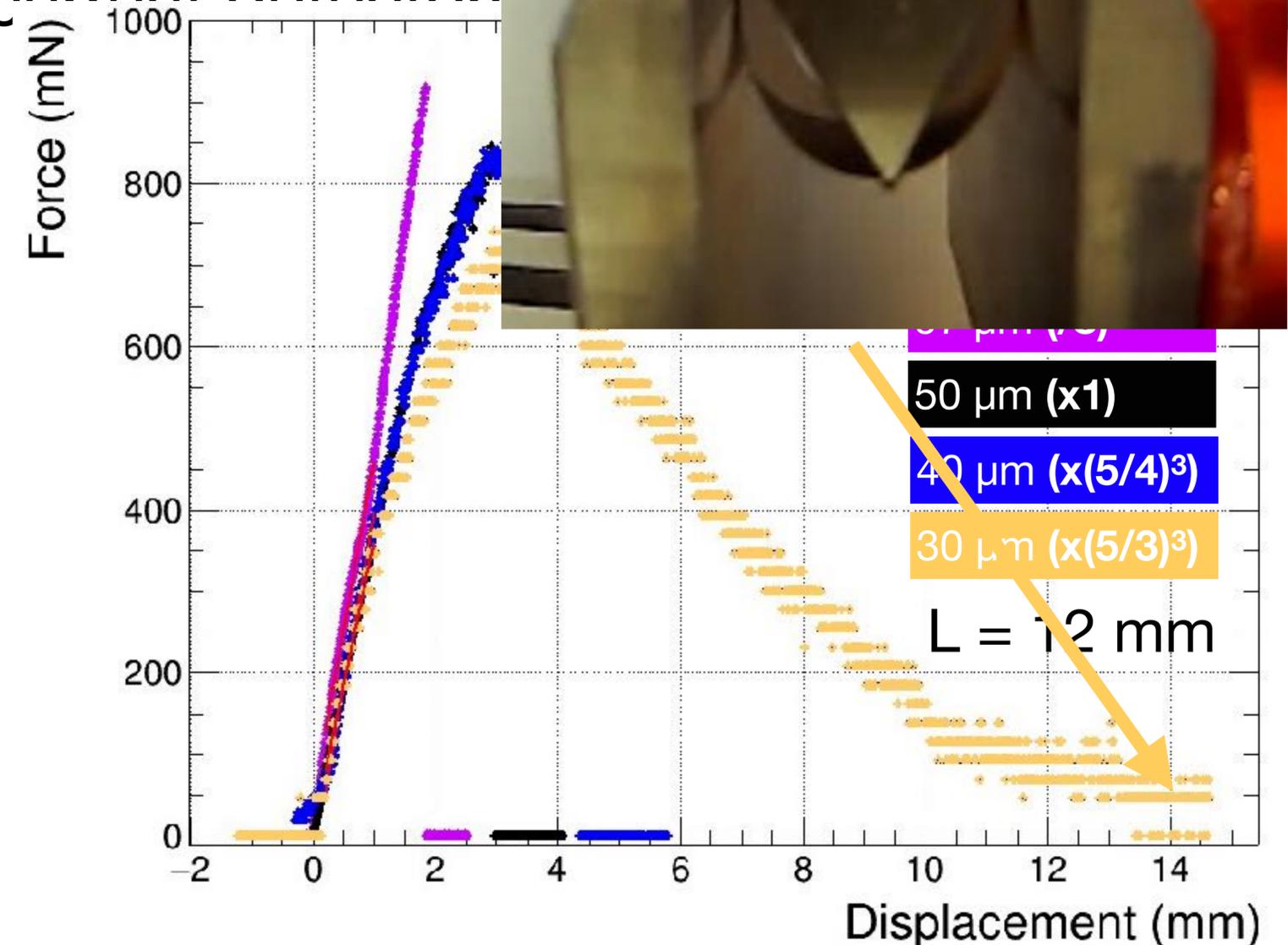
- ▶ **Monolith**
  - already
- ▶ **Bending**
  - large benefit from thinner sensors
- ▶ Breakage at smaller radii for thinner chips
  - again benefit from thinner sensors
- ▶ **Our target values are very feasible!**



There is quite some margin already at 50 μm!

# Flexibility of silicon

- ▶ **Monolithic Active Pixel Sensors** are quite flexible
  - already at thicknesses that are used for current detectors
- ▶ Bending force scales as  $(\text{thickness})^{-3}$ 
  - large benefit from thinner sensors
- ▶ Breakage at smaller radii for thinner chips
  - again benefit from thinner sensors
- ▶ **Our target values are very feasible!**



There is quite some margin already at 50  $\mu\text{m}$ !

# Bending of wafer-scale sensors procedure



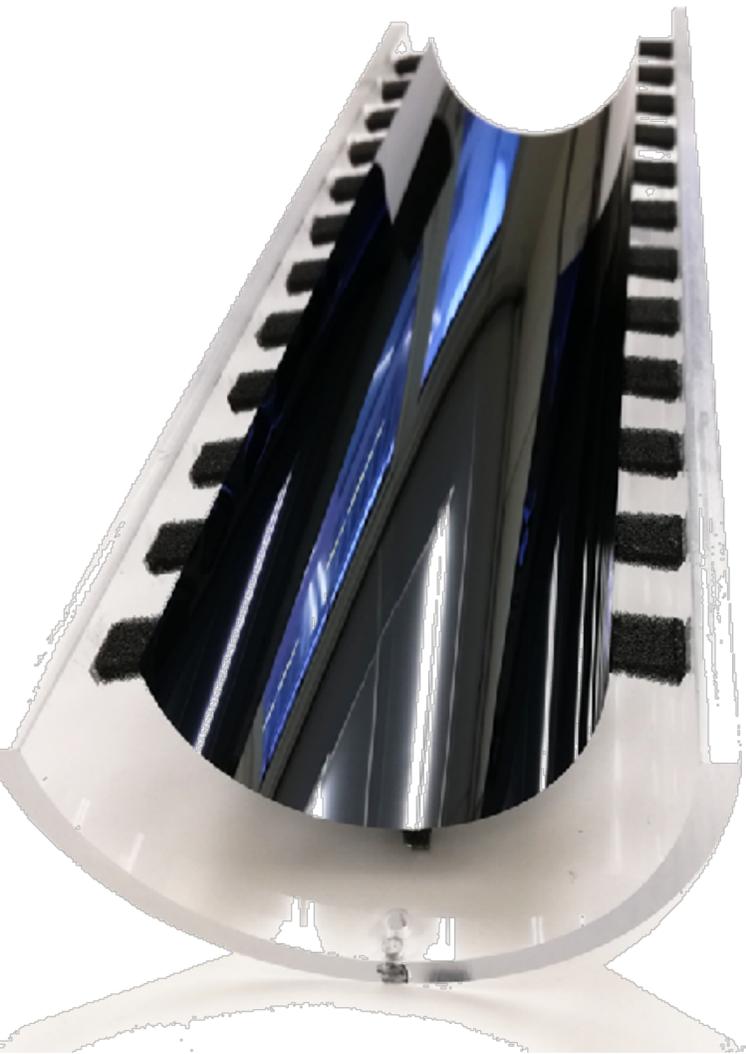
30 mm (L2)

50  $\mu$ m dummy Silicon

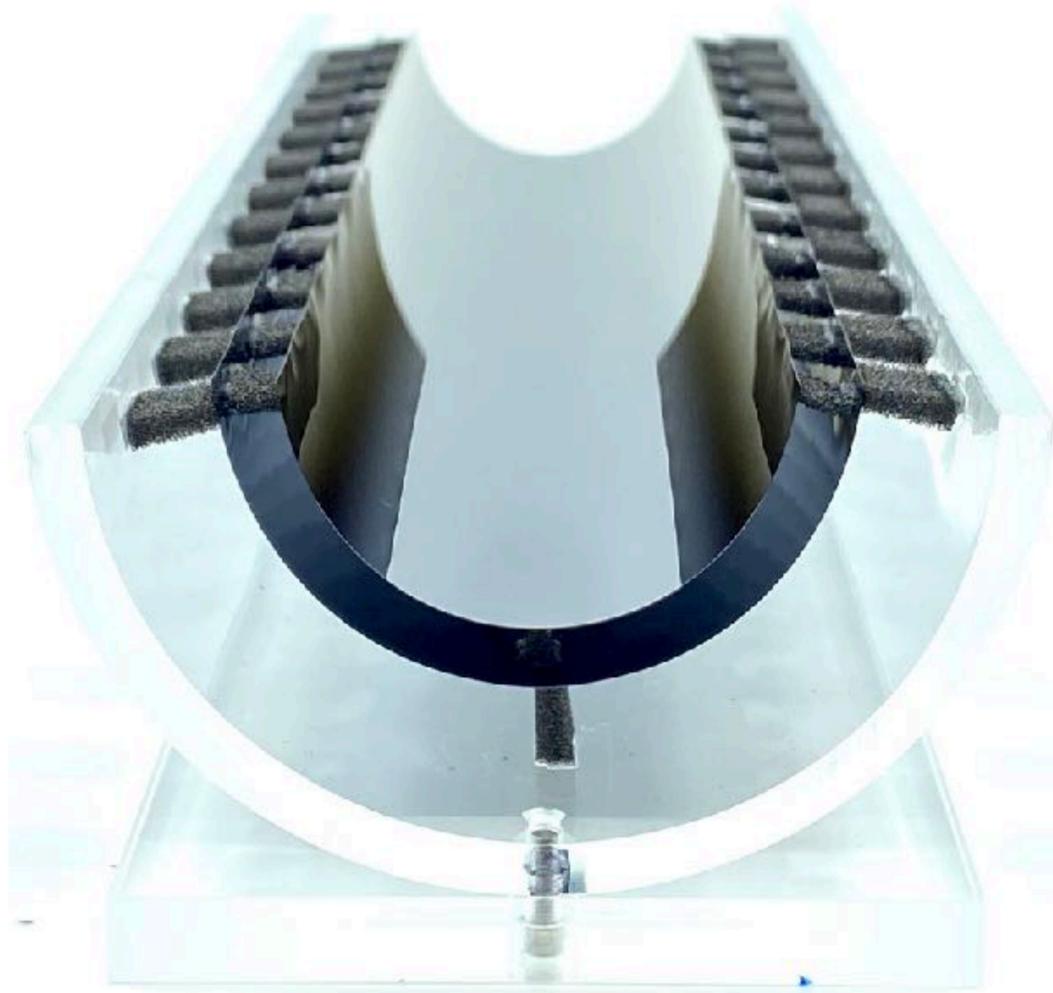
# Layer assembly



Layer 2



Layers 2+1



Layers 2+1+0



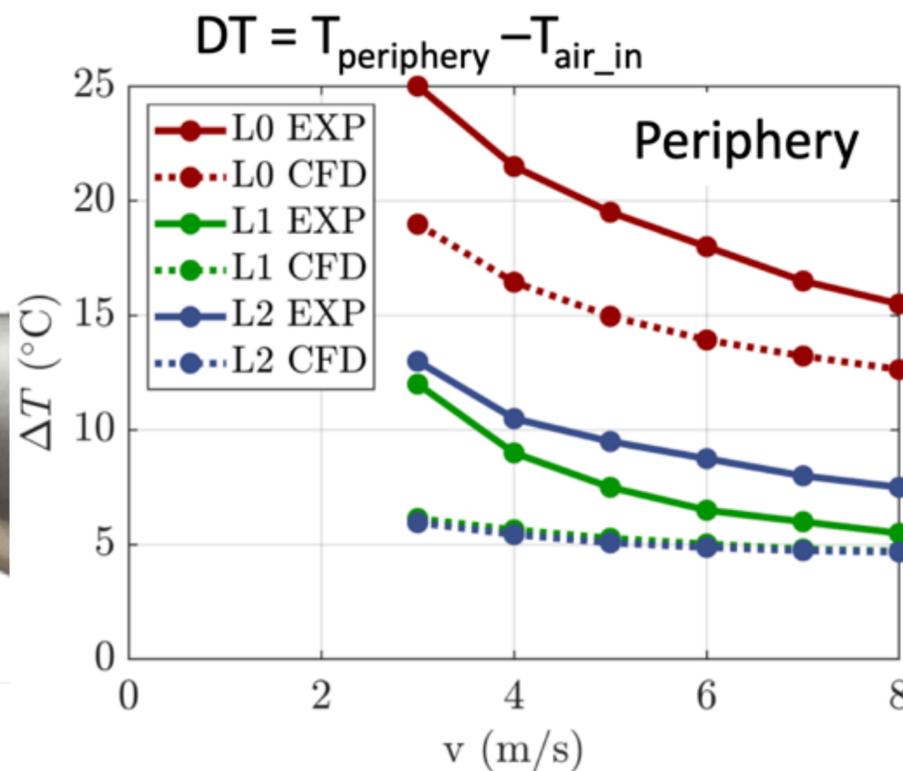
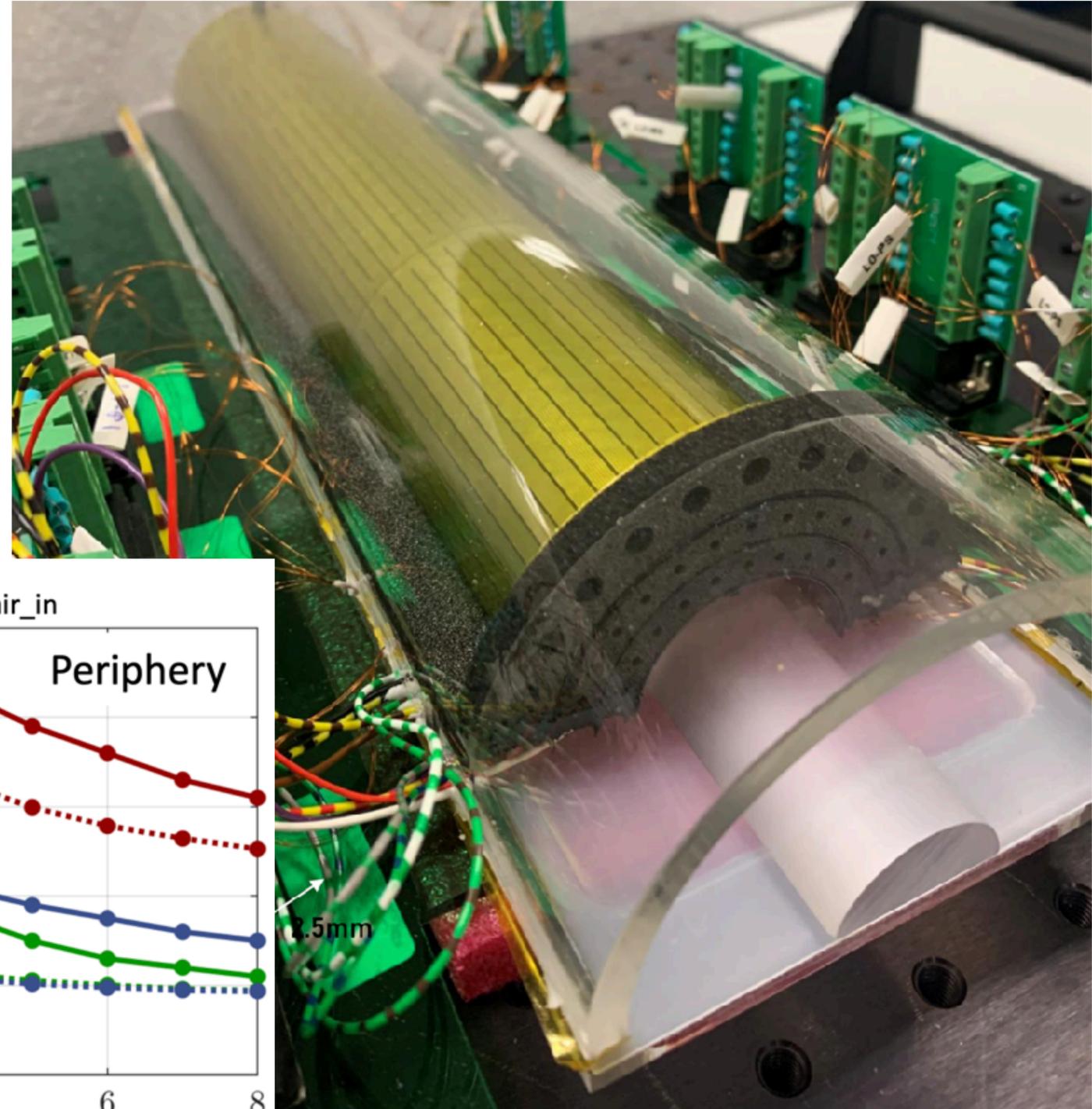
3-layer integration successful!

# R&D on air cooling

- ▶ A set of bread board models based on heating elements are being developed
- ▶ Placed in a custom wind tunnel, thermal and mechanical properties are studied

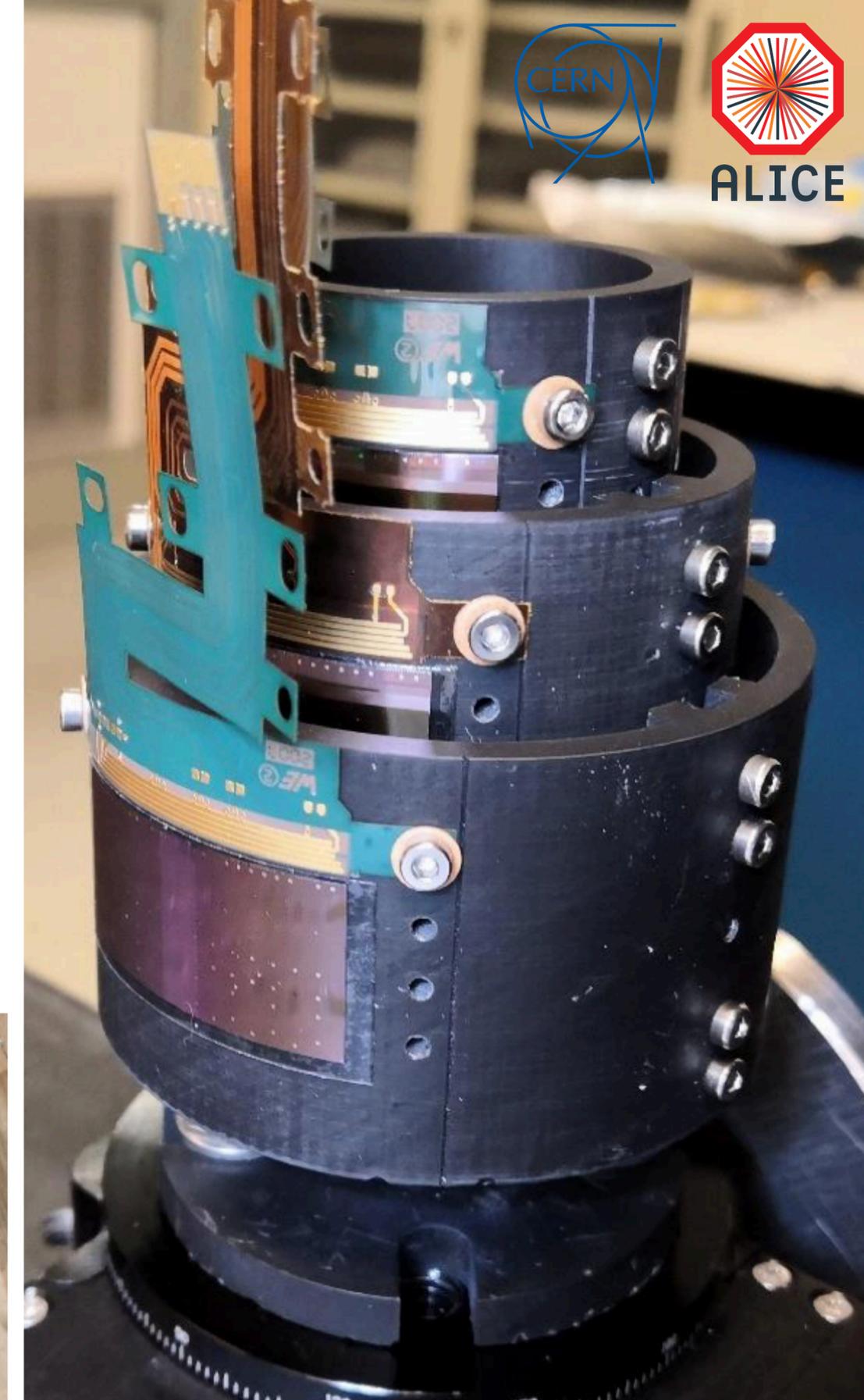
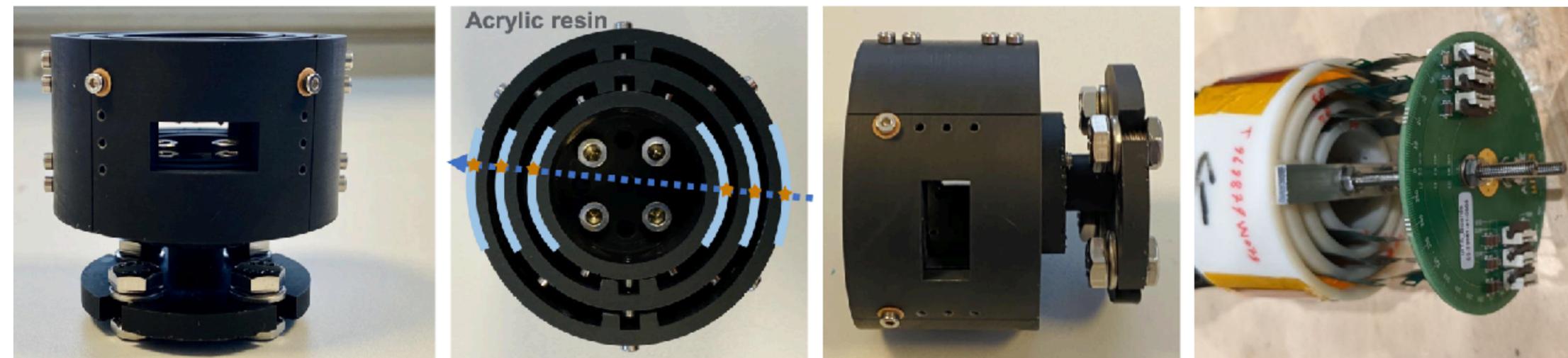


Wind tunnel



# Bent ALPIDEs

- ▶ A number of prototypes with bent ALPIDEs were produced
  - several different ways were explored (bending before bonding, or vice versa, different jigs)
  - “feeling” for handling thin silicon was gained
- ▶ By now, we have a full mock-up of the final ITS3, called “ $\mu$ ITS3”
  - 6 ALPIDE chips, bent to the target radii of ITS3



# Beam tests

1st paper doi:10.1016/j.nima.2021.166280

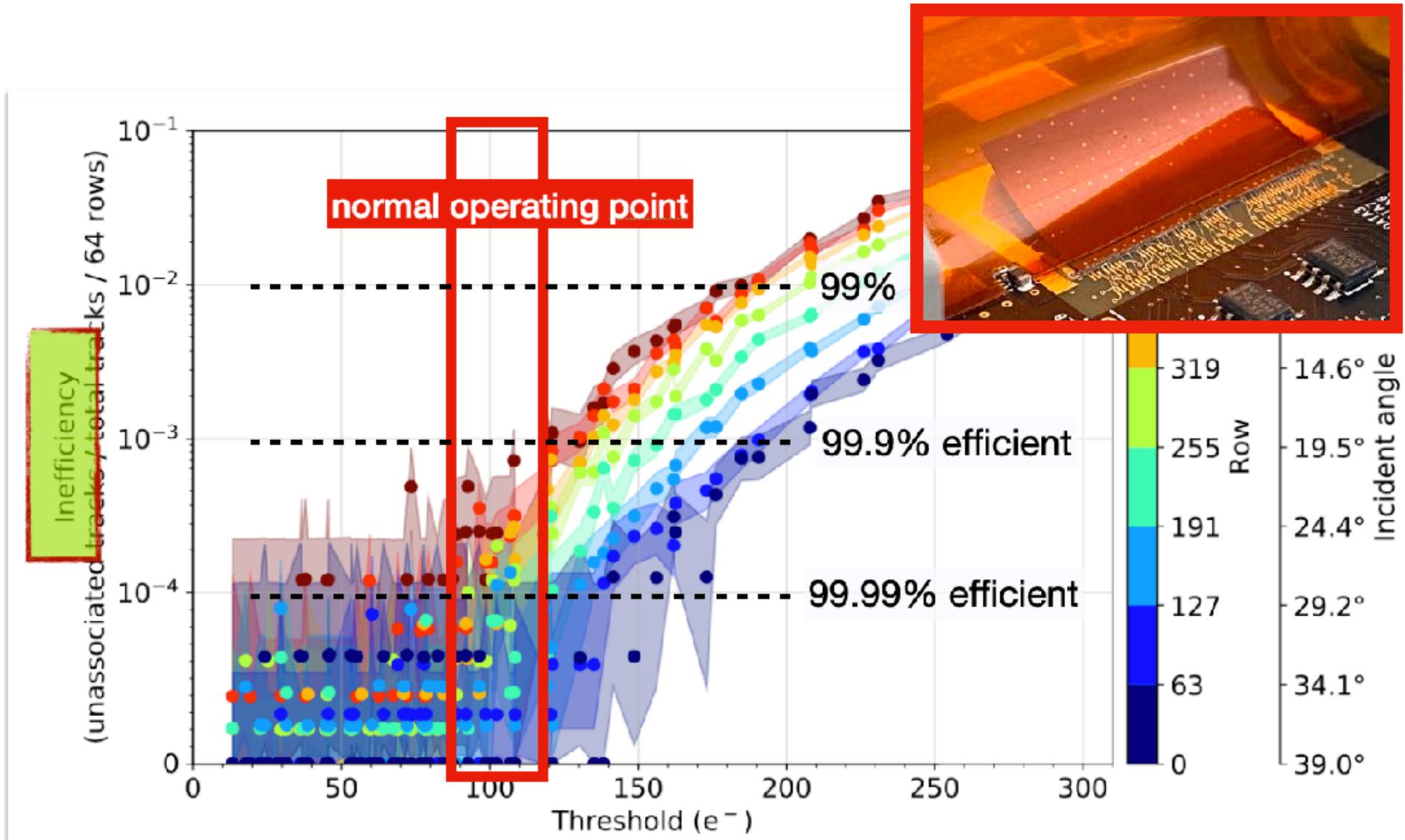


Fig. 10: Inefficiency as a function of threshold for different rows and incident angles with partially logarithmic scale ( $10^{-1}$  to  $10^{-5}$ ) to show fully efficient rows. Each data point corresponds to at least 8k tracks.



Nuclear Instruments and Methods  
in Physics Research Section A:  
Accelerators, Spectrometers,  
Detectors and Associated  
Equipment



Available online 10 January 2022, 166280  
In Press, Journal Pre-proof

## First demonstration of in-beam performance of bent Monolithic Active Pixel Sensors

ALICE ITS project <sup>1</sup>

Show more

Share Cite

<https://doi.org/10.1016/j.nima.2021.166280>

Get rights and content

Clearly proving that bent MAPS are working!



ALICE

# TPSCo 65 nm CIS

# TPSCo 65 nm CIS

## reasons for migration from TJ 180 nm CIS

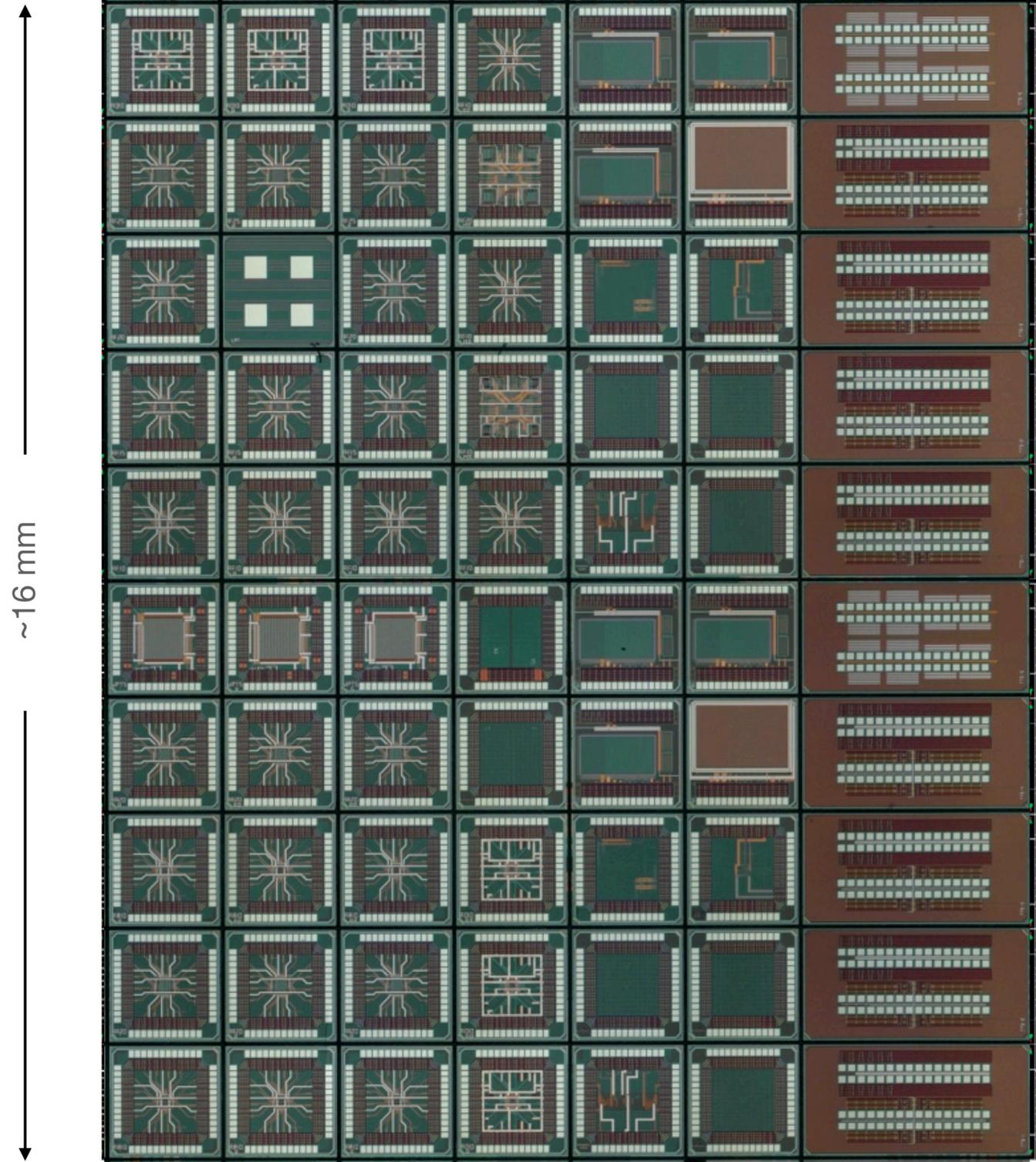


- ▶ ALICE by now long standing experience with **Tower Semiconductor** (aka “TowerJazz”), using their **180 nm CIS** process
  - we produced and tested >70k sensors for ITS2
  - we optimised the process together with the foundry to reach full depletion (not used for ITS3, but then followed up later by several groups)
- ▶ The **65 nm CIS** of **Tower Partners Semiconductor (TPSCo)** offers:
  - **larger wafers:** 300 mm instead of 200 mm, single “chip” is enough to equip an ITS3 half-layer
  - **smaller structure sizes:** *potentially*
    - lowering power consumption
    - increasing spatial resolutions
    - increasing in-pixel circuitry
    - increasing yield

# First submission in TPSCo 65 nm CIS



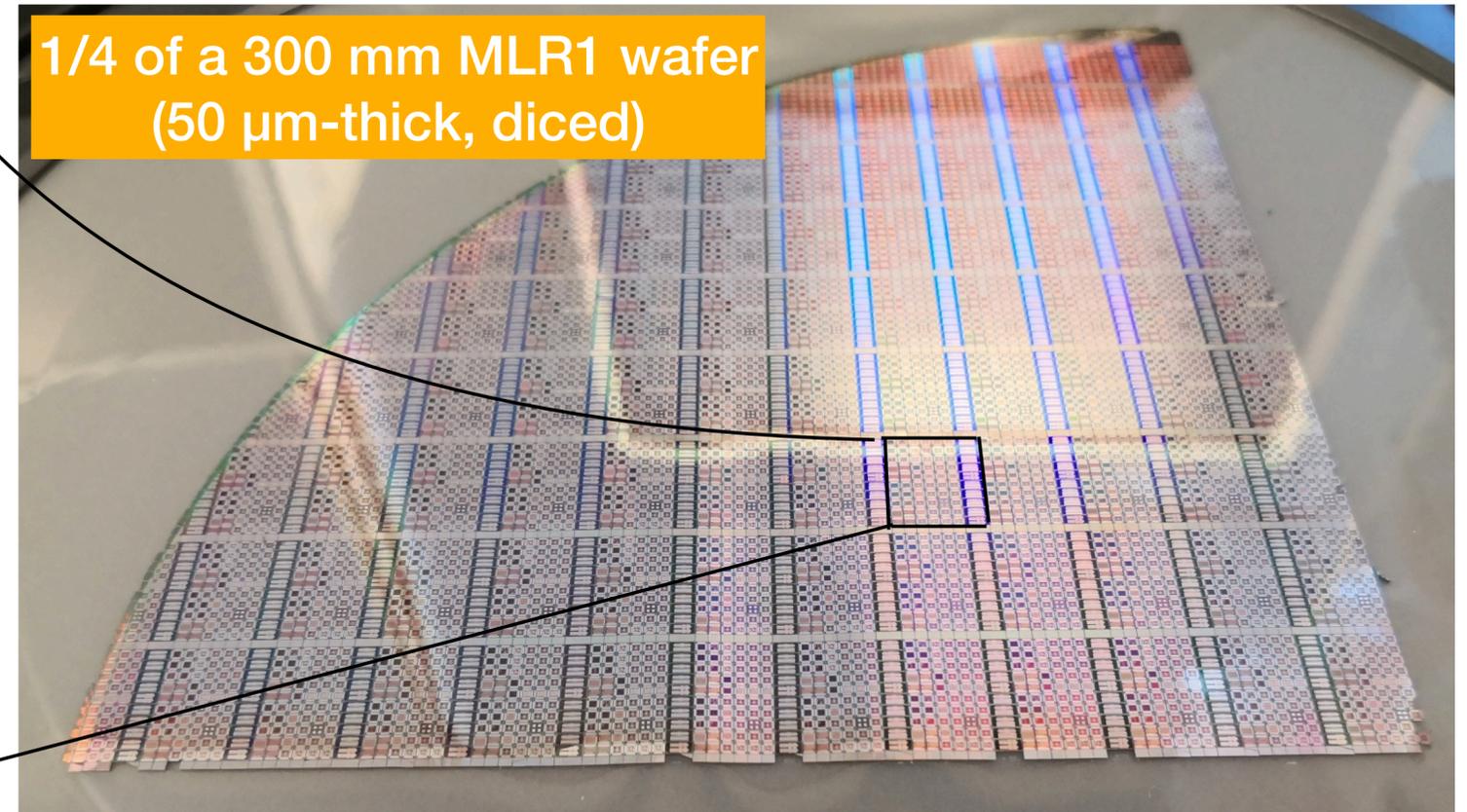
~12 mm



~16 mm

- ▶ Submission together with CERN EP R&D WP 1.2
  - contains many test chips (transistor test structures, DACs, analog pixel matrices, digital pixel matrices, ...)
- ▶ Fully processed wafers available since **summer 2021**
- ▶ Chips are now thinning/diced/picked in large quantities
- ▶ Tests are ongoing at several institutes and groups

1/4 of a 300 mm MLR1 wafer  
(50  $\mu\text{m}$ -thick, diced)

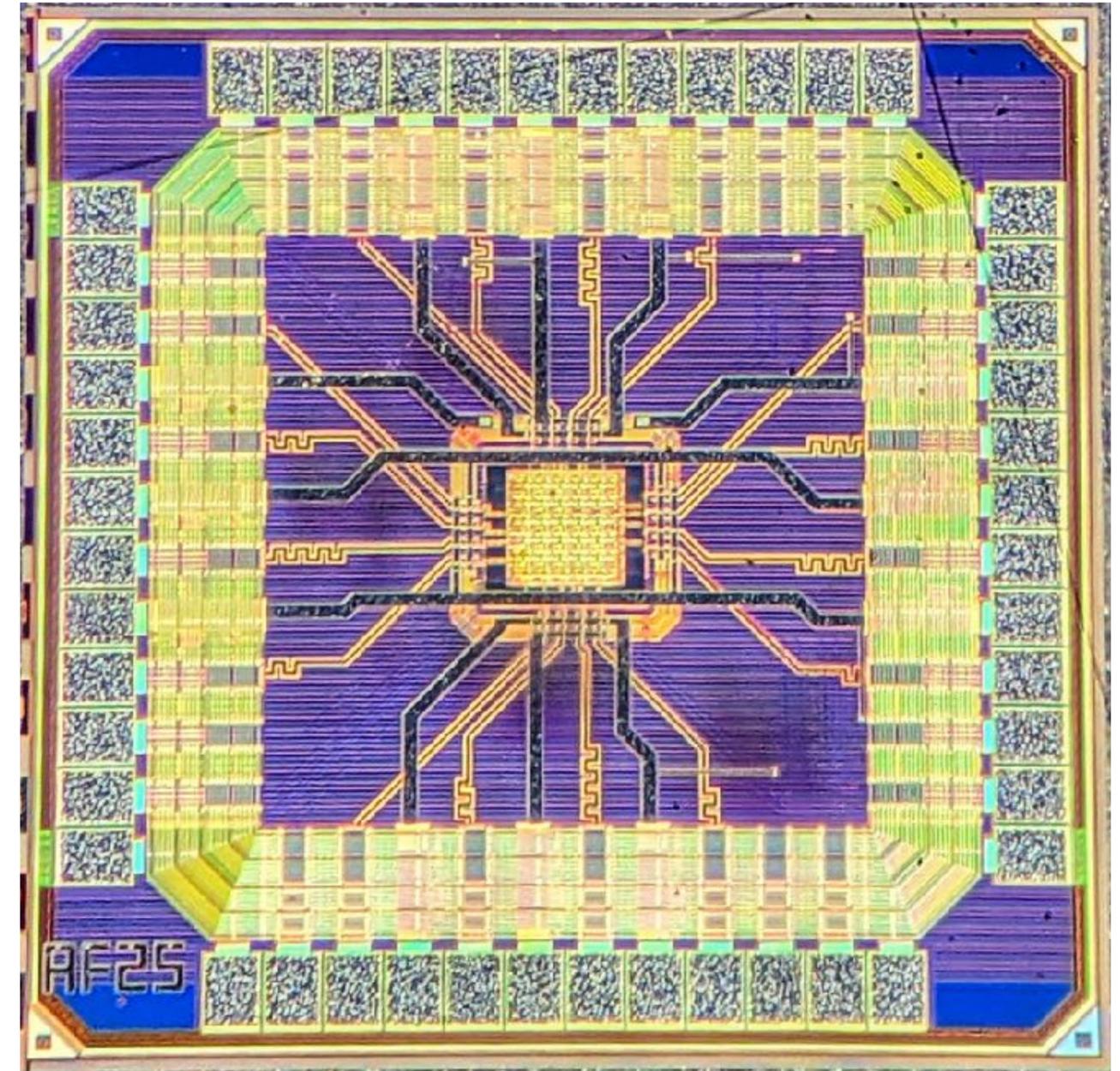


# Analog Pixel Test Structure (APTS)



## overview

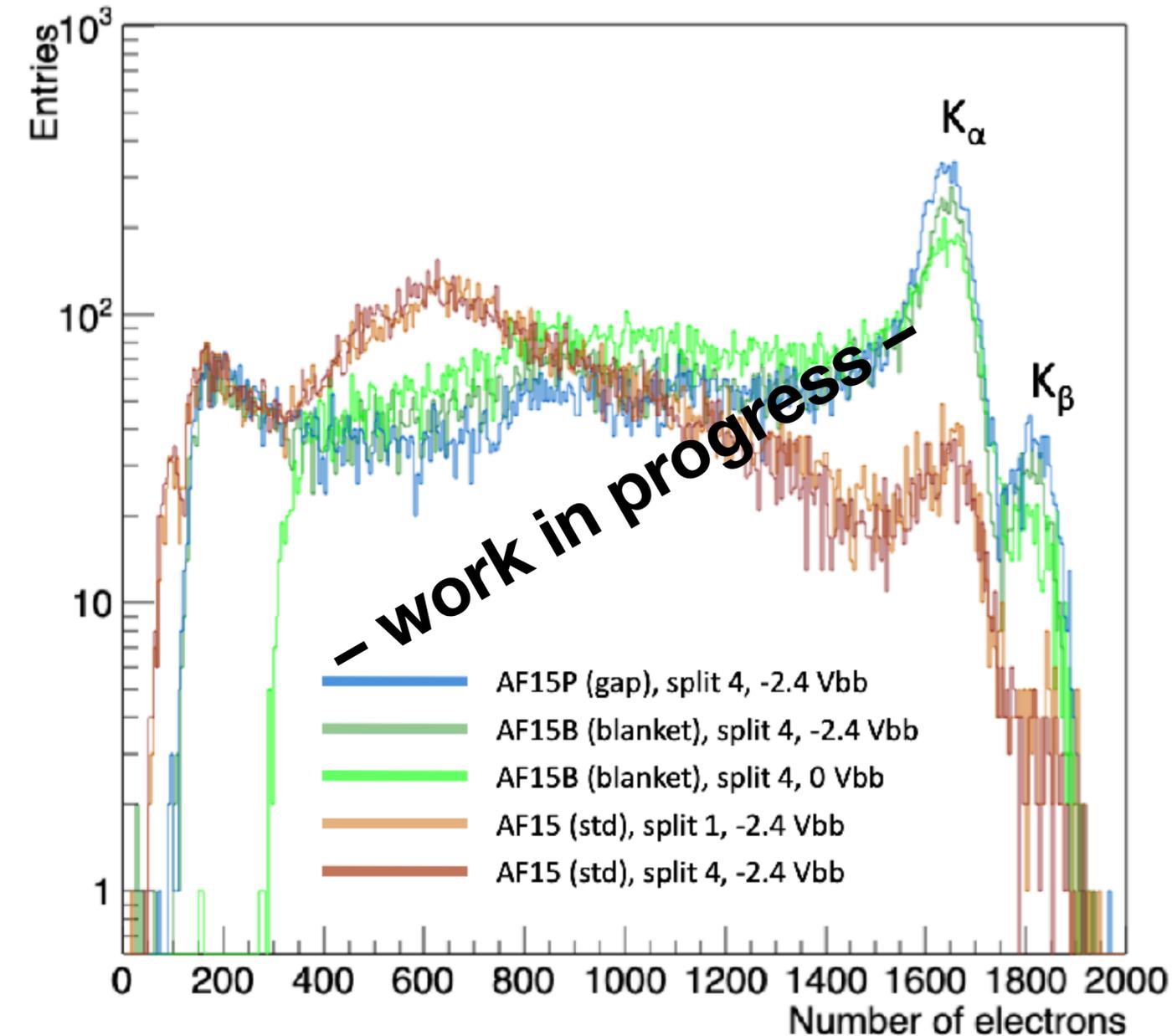
- ▶ The analog pixel test structure (APTS)
  - 6x6 pixels (central 4x4 read out)
  - different pitches: **10, 15, 20, 25  $\mu\text{m}$**
  - different implant geometries
  - different output drivers
- ▶ Allows for very detailed mapping of parameters space
  - important e.g. in view of larger pixels
  - also key to verify and tune simulation models



# APTS lab results

## process optimisation: charge collection/sharing

- ▶ Already in the first run in 65 nm process modifications were done together with the foundry
  - excellent collaboration with the foundry
  - this took several years in the 180 nm
- ▶ This allows to engineer/tune the charge charging and collection times to some extent
- ▶ A detailed study will allow to choose the best trade-off for the vertex detector, outer tracker

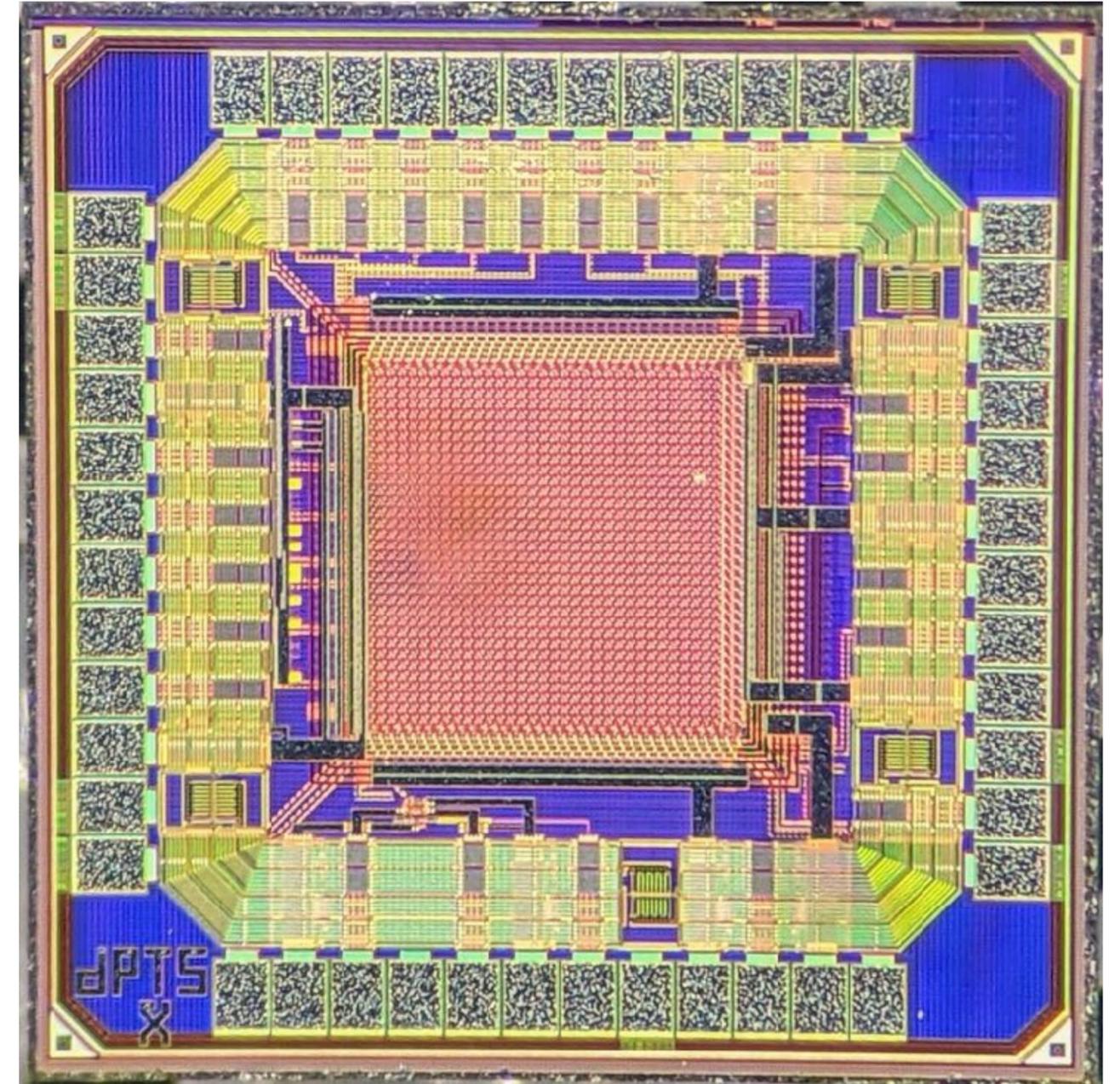


# Digital Pixel Test Structure (DPTS)

## overview



- ▶ The digital pixel test structure (DPTS)
  - 32x32 15  $\mu\text{m}$  pitch pixels
- ▶ Includes full digital front-end and readout
- ▶ Studied now in detail, shows excellent performance parameters (**preliminary**):
  - Efficiency: >99%
  - Time resolution: O(10ns)
  - Radiation hardness: OK for ALICE
  - Spatial resolution: O(3-4  $\mu\text{m}$ )
- ▶ Silicon-proven building block for larger chips!

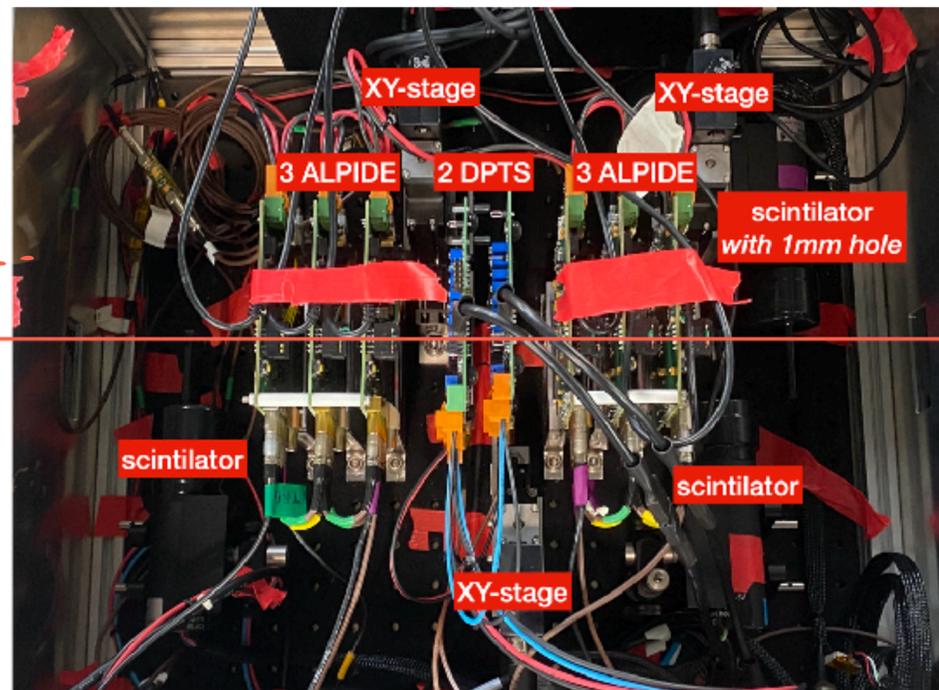
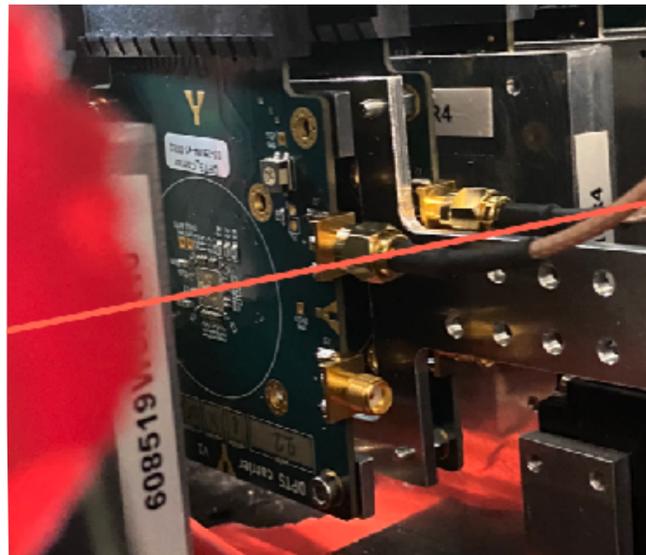


# DPTS test beam results

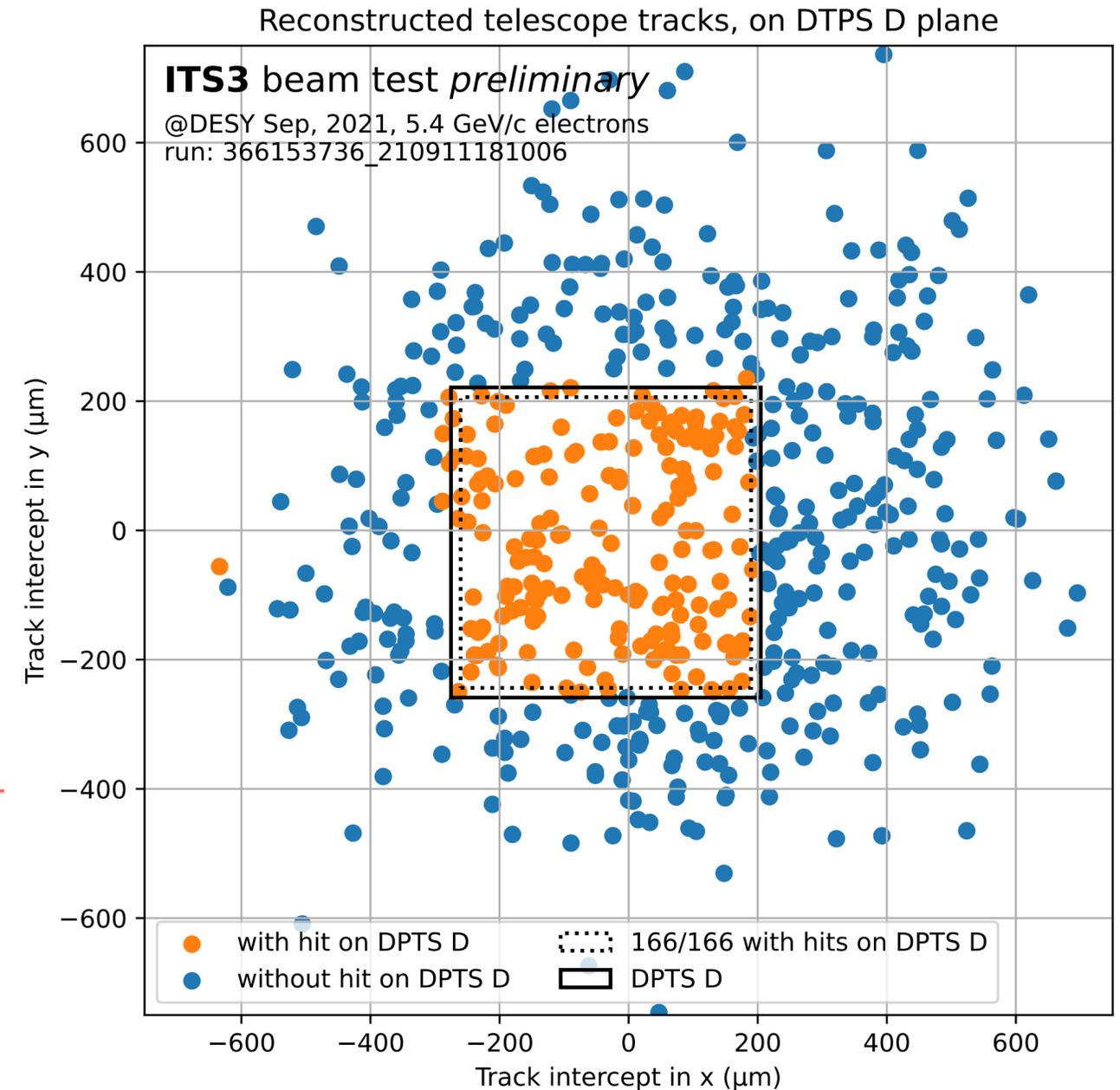
## detection efficiency



- ▶ 100% detection efficiency at first shot
- ▶ by now validated at >5 beams campaigns
- ▶ including irradiated samples (preliminary)



1 PMT (trg) 3 ALPIDE (ref) 2 DPTS (DUT) 3 ALPIDE (ref) 1 PMT (trg) 1 PMT (anti)



**DPTS D**  
 wafer: 22  
 chip: 1  
 version: 1  
 split: 4 (opt.)  
 $V_{pwell} = -1.2\text{V}$   
 $V_{sub} = -1.2\text{V}$   
 $I_{reset} = 10\text{pA}$   
 $I_{bias} = 100\text{nA}$   
 $I_{biasn} = 10\text{nA}$   
 $I_{db} = 100\text{nA}$   
 $V_{casn} = 300\text{mV}$   
 $V_{casb} = 250\text{mV}$

# Towards the final sensor



## next submission “ER1”

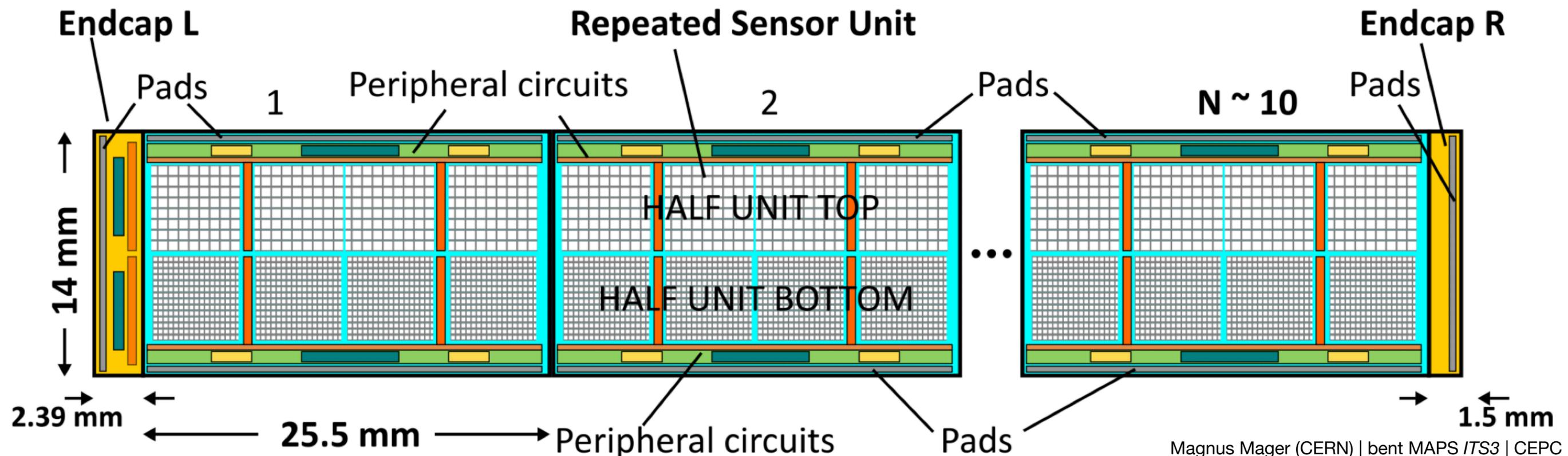
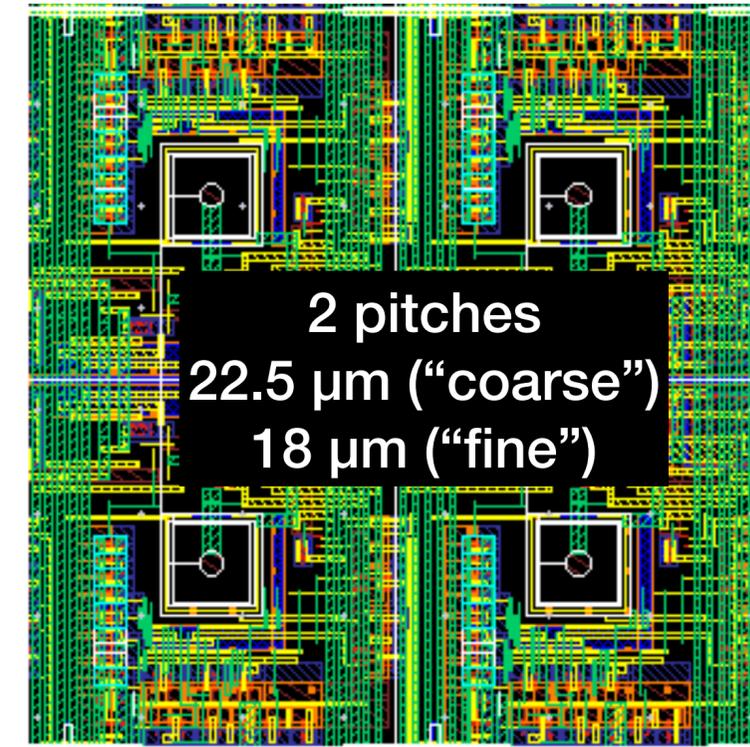
- ▶ **Floor plan** compatible with stitching **worked out** in close collaboration with foundry
- ▶ **Mock submission** happened **Dec 2021**
  - crucial step to verify stitching constraints
- ▶ **Designs** (ITS3 + CERN EP R&D WP1.2) include:
  - the large **ITS3 stitching demonstrator** (“MOSS”)
  - an alternative stitching architecture (“MOST”)
  - several small chips with building blocks and pixel and radiation test structures
- ▶ Designs are converging:
  - plan to **submit before summer 2022**
- ▶ Preparations for **post-processing** and **testing ongoing**



# ER1

## MOSS: ITS3 stitching demonstrator

- ▶ Fully functional sensor (with diodes, front-end, readout)
  - taking advantage of Si-proven parts from MLR1
  - but not integrating all building blocks and functionality of final sensor, yet
- ▶ Different densities (itches) to study impact onto yield
- ▶ Several testing options to study voltage drops and possible defects

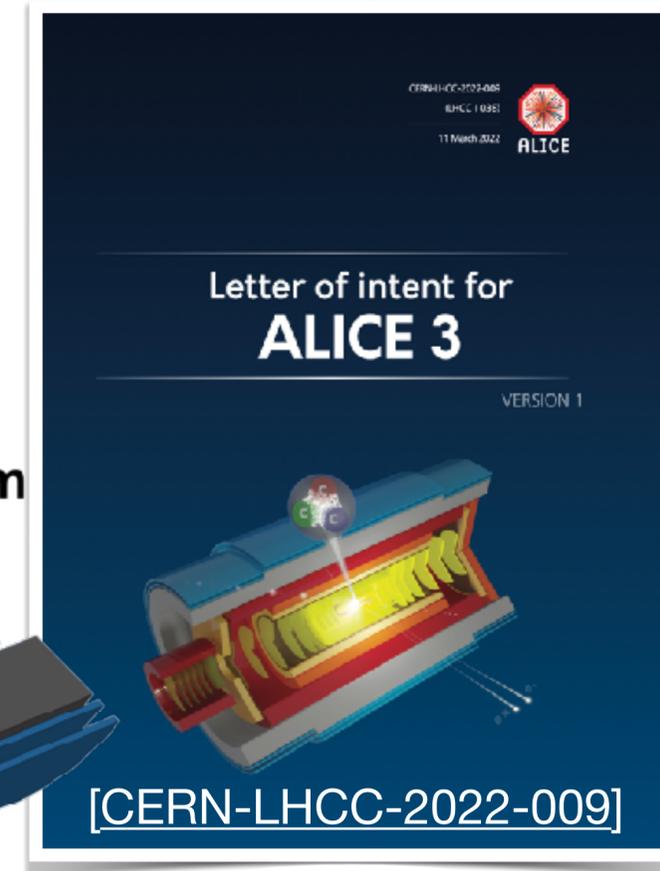
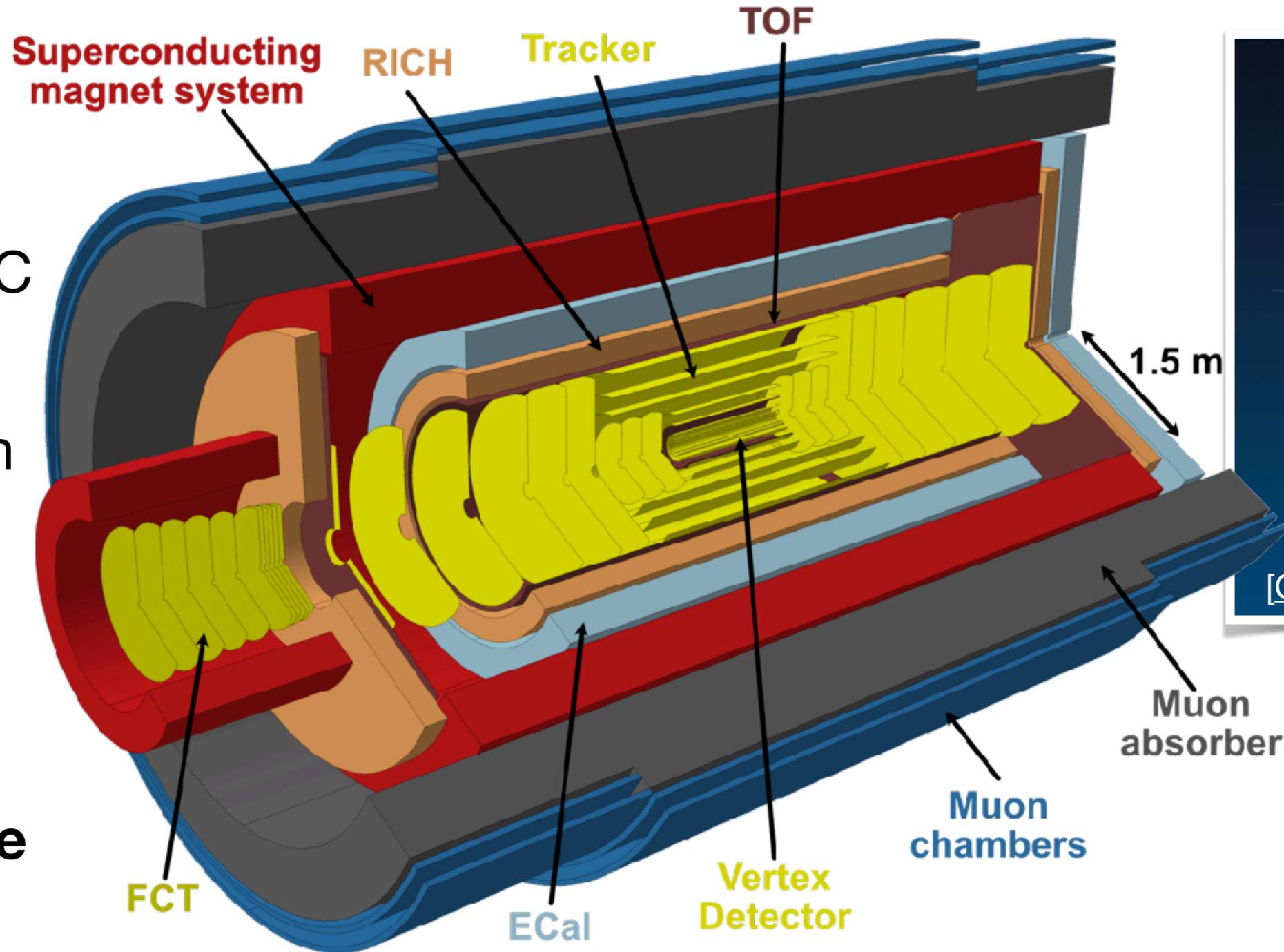


# Outlook

## ALICE 3



- ▶ ALICE proposes to build a completely new detector in LHC LS4 (2033-34)
- ▶ It will heavily rely on silicon detectors
- ▶ Central part: a **60 m<sup>2</sup> MAPS tracker**
  - with **in-beampipe** vertex layers



Letter of Intent very positively evaluated by LHCC → R&D programme ramping up!

# Summary



- ▶ **ALICE** has a history in developing MAPS and will continue to do so:
  - **ITS2** (10 m<sup>2</sup>, 12.5 GPixel) is installed and taking data
  - R&D for **ITS3** is ongoing and well on track
  - **ALICE 3** will scale the effort up by another order of magnitude
- ▶ Requirements for a **Lepton Collider** are very similar to those for **ALICE ITS3**
  - ITS3 can be seen as the demonstrator/prototype/concept detector for lepton facilities
  - even better: ITS3 will be a real full-scale detector facing and addressing integration issues
- ▶ Very **exciting times** for MAPS are ahead of us!



*Thank you!*

